Module 1: Devices
Diodes, MOS transistors, models

Goal of this chapter

- Present intuitive understanding of device operation
- Introduction of basic device equations
- Introduction of models for manual analysis
- Introduction of models for SPICE simulation
- Analysis of secondary and deep-sub-micron effects
- Future trends

Outline

- Semiconductor Physics
- The diode
  - Depletion, I-V relations, capacitance,
- The MOS transistor
  - First glance, threshold, I-V relations, models
  - Dynamic behavior (capacitances), resistances,
- Process variations

Course Material for Devices

Chapter 3

P = primair, I = Illustratie, O = overslaan

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(1) Vervangend studiemateriaal voor dynamisch gedrag in syllabus

Modeling

- An abstraction of (the properties) of something to help understanding and predicting its behavior
- Domain Specific: weather, climate, economy, stock market, ...
- Different models for something to answer different questions
- Black-Box modeling vs. Physically Based

- After Einstein: a model should be as simple as possible, but not simpler

Semiconductor Physics

- **All electrical behavior is determined by underlying physics**
- **This course is not about the physics**
- **But some small amount of background information helps built intuition**
- **Intuition is what an engineer/designer needs most**
- **Also see S&G Chapter 2.**

Periodic System

1 H																	2 He
3 Li	4 Be											5 B	6 C	7 N	8 O	9 F	10 Ne
11 Na	12 Mg											13 Al	14 Si	15 P	16 S	17 Cl	18 Ar
19 K	20 Ca	21 Sc	22 Ti	23 V	24 Cr	25 Mn	26 Fe	27 Co	28 Ni	29 Cu	30 Zn	31 Ga	32 Ge	33 As	34 Se	35 Br	36 Kr
37 Rb	38 Sr	39 Y	40 Zr	41 Nb	42 Mo	43 Tc	44 Ru	45 Rh	46 Pd	47 Ag	48 Cd	49 In	50 Sn	51 Sb	52 Te	53 I	54 Xe
55 Cs	56 Ba	57 La	72 Hf	73 Ta	74 W	75 Re	76 Os	77 Ir	78 Pt	79 Au	80 Hg	81 Tl	82 Pb	83 Bi	84 Po	85 At	86 Rn
87 Fr	88 Ra	89 Ac	104 Rf	105 Db	106 Sg	107 Bh	108 Hs	109 Mt	110 Uun								

58 Ce	59 Pr	60 Nd	61 Pm	62 Sm	63 Eu	64 Gd	65 Tb	66 Dy	67 Ho	68 Er	69 Tm	70 Yb	71 Lu
90 Th	91 Pa	92 U	93 Np	94 Pu	95 Am	96 Cm	97 Bk	98 Cf	99 Es	100 Fm	101 Md	102 No	103 Lr

Legend

Li Solid — Cs Liquid — Ar Gas — No Synthetic

Alkali metals — Alkali earth metals — Transition metals — Rare earth metals

Other metals — Noble gases — Halogens — Other nonmetals

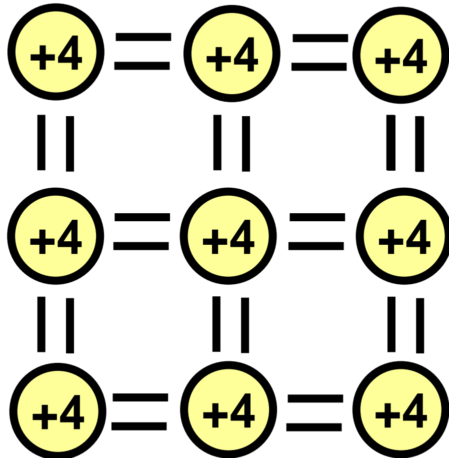
http://www.chemicool.com/

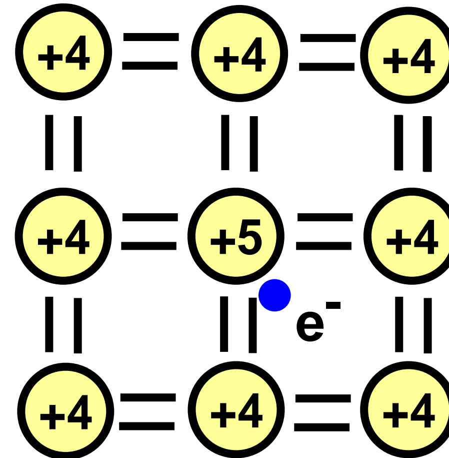
Periodic System

Name	Symbol	#	Valence
Silicon	Si	14	4
Boron	B	5	3
Phosphor	P	15	5
Arsenic	As	33	5
Germanium	Ge	32	4

Semiconductor Physics

See also Tipler (BKV) 38.5





- Intrinsic Si
- Ideal crystal structure
- Valence 4
- almost no free carriers
- almost no conduction

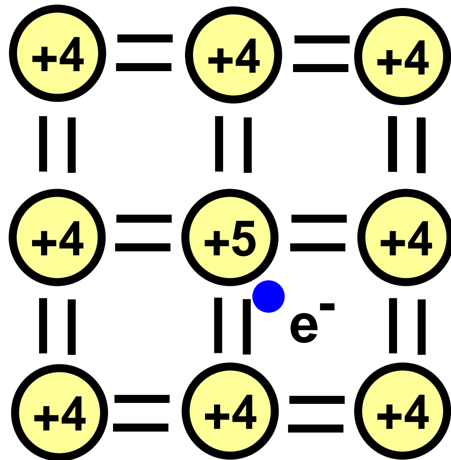
$$[n] = [p] = n_i = 1{,}5.10^{10} / cm^3$$

at 300 K for silicon

- doping with valence 5 atoms (Phosphor, Arsenic) introduces "loose electrons"
- electron donor
- conductivity depends on doping level

$$n.p = n_i^2 \quad (\text{in equilibrium})$$

Semiconductor Physics



- doping with valence 5 atoms (Phosphor, Arsenic) introduces "loose electrons"
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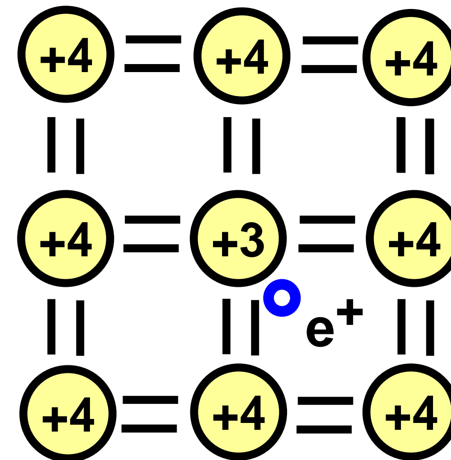
- conductivity depends on doping level



- doping with valence 3 atoms (Boron) introduces "loose holes"
- electron acceptors
- hole conductivity lower than electron conductivity

Semiconductor Physics

Si in equilibrium : $n.p = n_i^2 = 2.25 \times 10^{20}$ at 300K

Intrinsic Si : $n = p = n_i$

$N_D >> N_A$

Electron donors: As, P

n-type Si

$n \approx N_D, p = n_i^2 / n$

Electrons: majority carriers

Holes: minority carriers

Resistive material

Conductivity depends on N_D

$N_A >> N_D$

Electron acceptors: B

p-type Si

$p \approx N_A, n = n_i^2 / p$

Holes: majority carriers

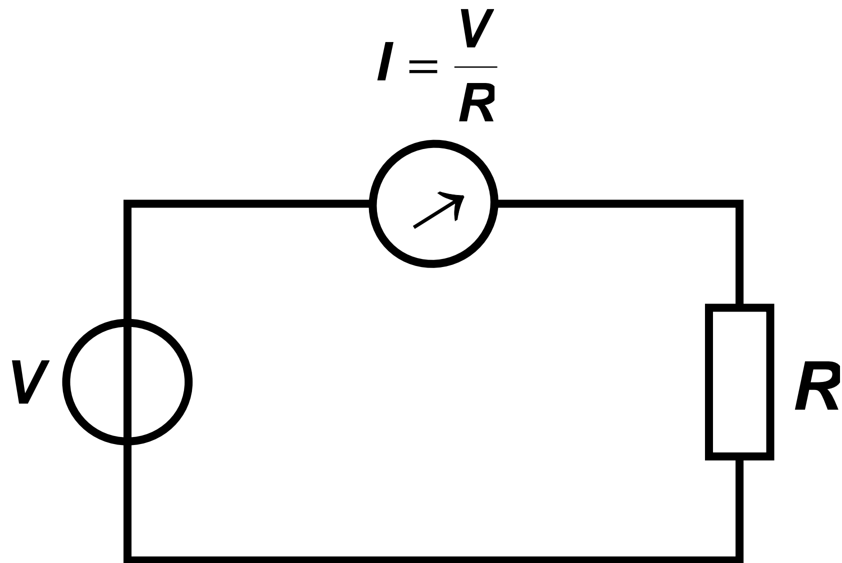
Electrons: minority carriers

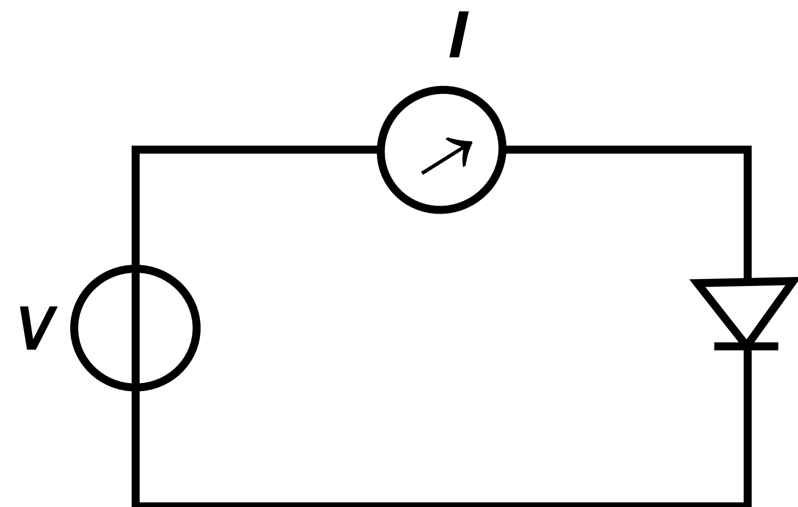
Hole conductivity lower than electron conductivity

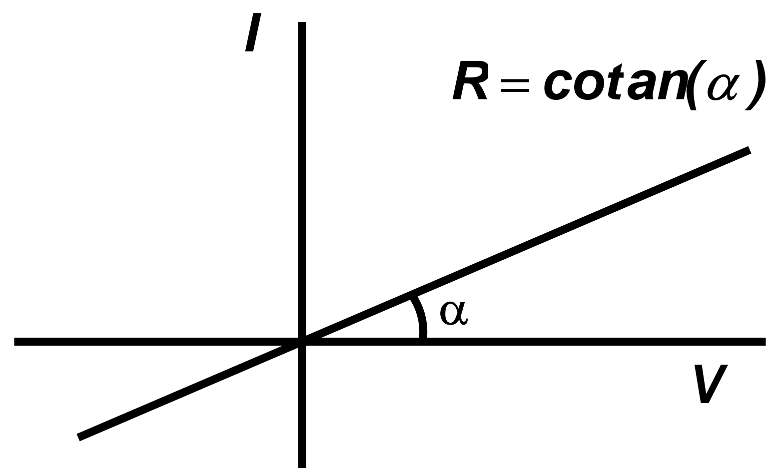
The diode

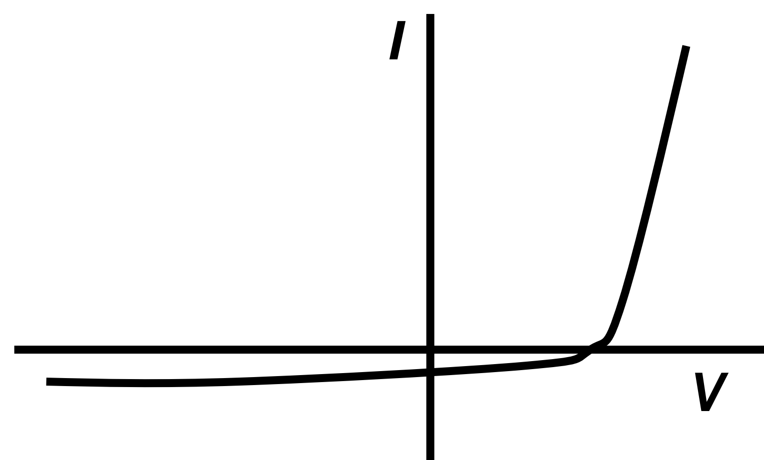
- **Depletion, I-V relations, capacitance,**

The diode: non-linear resistance



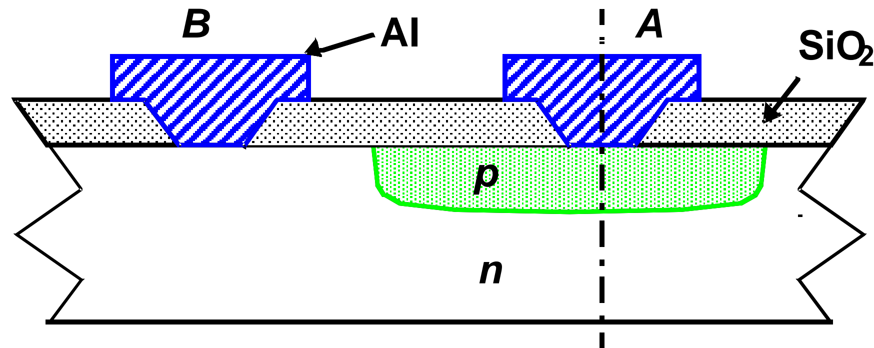




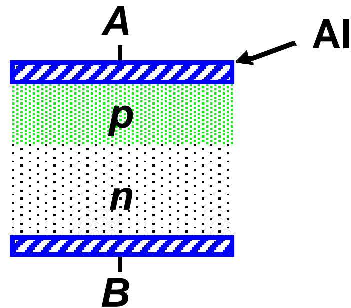


The Diode

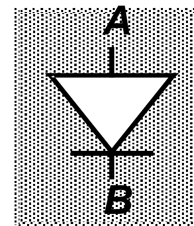
See also Tipler (BKV) 38.6



Cross-section of *pn*-junction in an IC process



One-dimensional representation



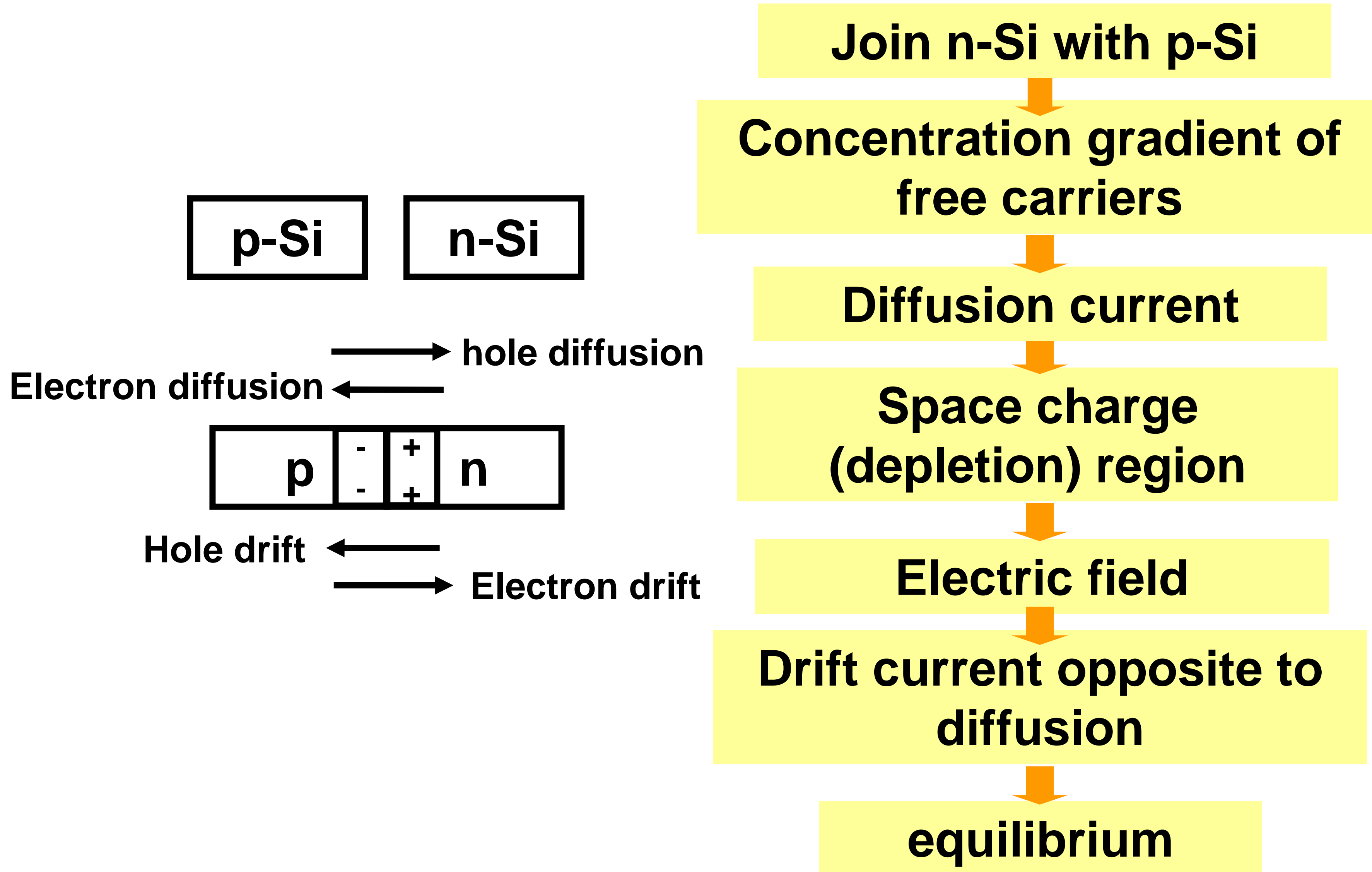
Anode

Cathode

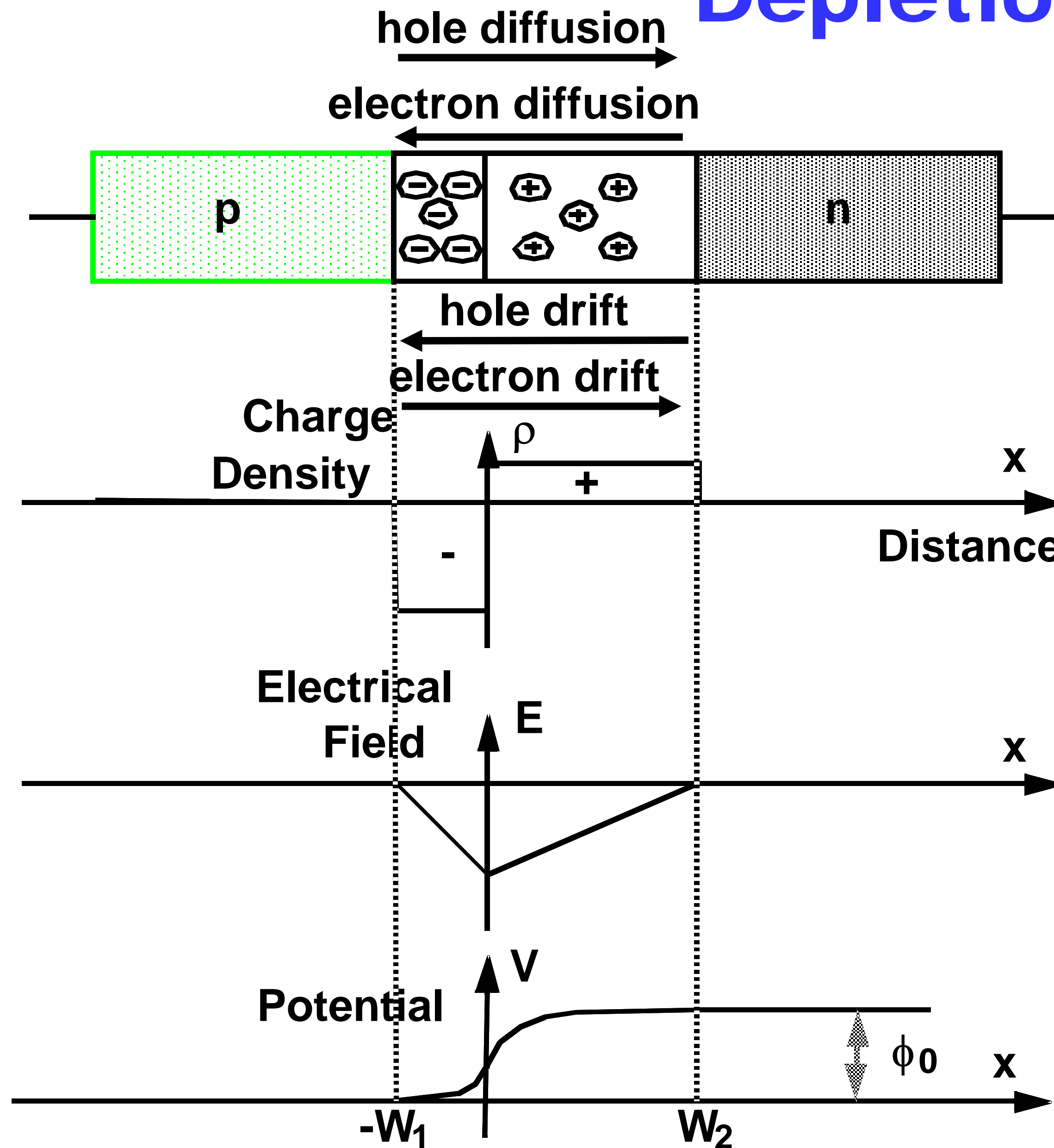
diode symbol

Diode is abundant as MOS source/drain

Ideal Diode, Abrupt pn junction
Intuitive Description



Depletion Region



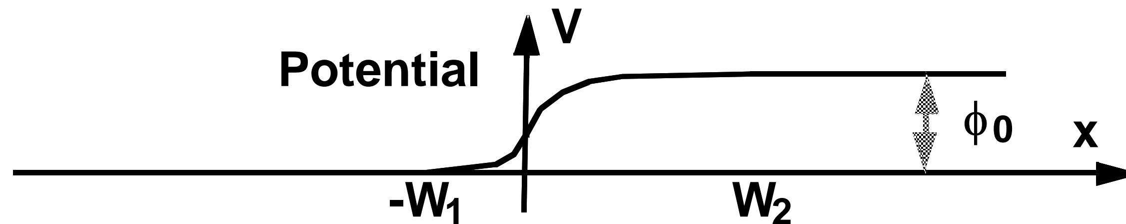
(a) Current flow.

(b) Charge density.

(c) Electric field.

(d) Electrostatic potential.

Conduction



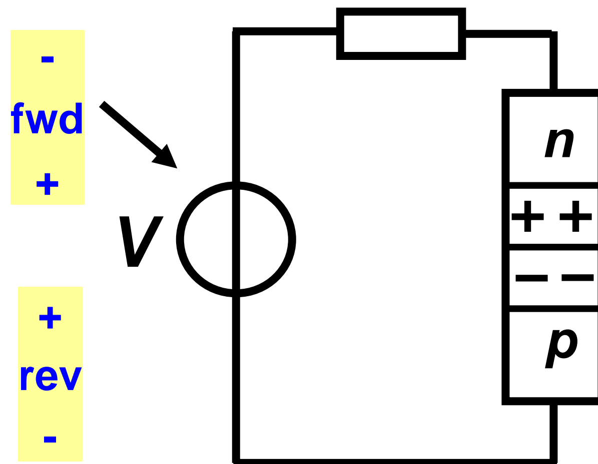
Typical N_A, N_D:
10^{15} … 10^{17}/cm³,
ϕ_0 around 0.6 V

Built-in Potential

$$\phi_0 = \phi_T \ln\left[\frac{N_A N_D}{n_i^2}\right]$$

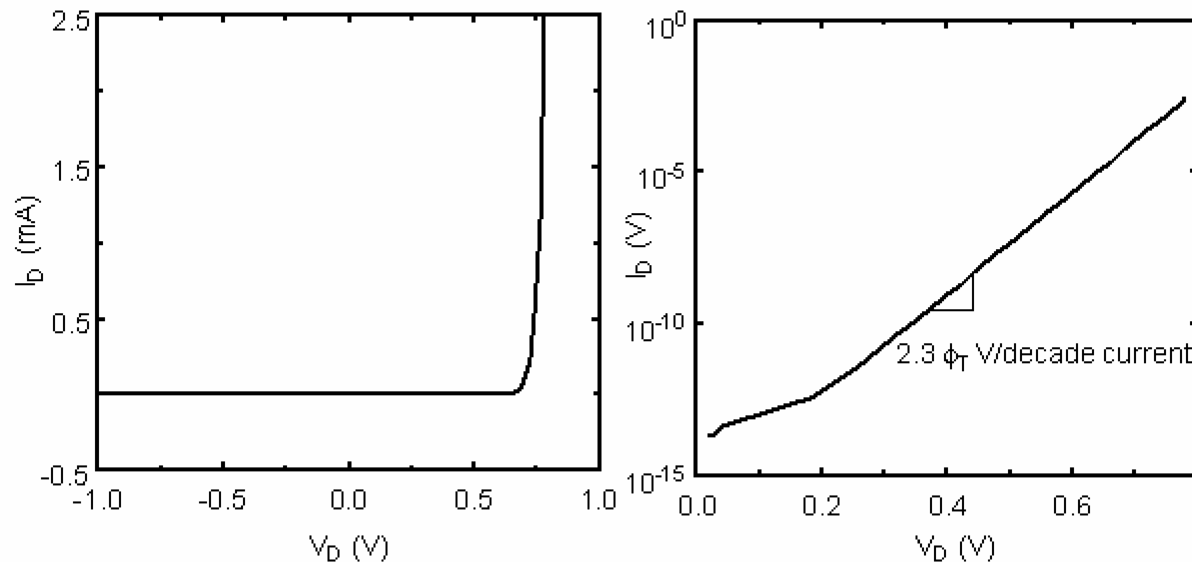
Thermal voltage

$$\phi_T = \frac{kT}{q} = 26\,mV \text{ at } 300\,K$$



- By applying an external voltage, width of depletion region can be changed
- Forward: becomes smaller and smaller, finaly conduction
- Reverse: becomes wider and wider => no conduction

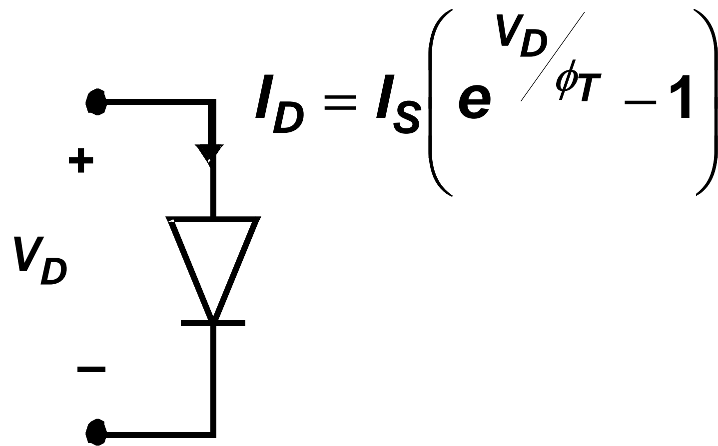
Diode Current

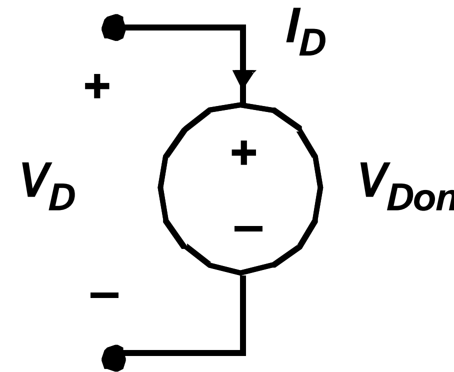


$$I_D = I_S\left(e^{V_D/\phi_T} - 1\right)$$

- I_S: **Saturation current**
- **Proportional to diode area**
- **Depends on doping levels,**
  and widths of neutral regions
- **Usually determined empirically**

Models for Manual Analysis

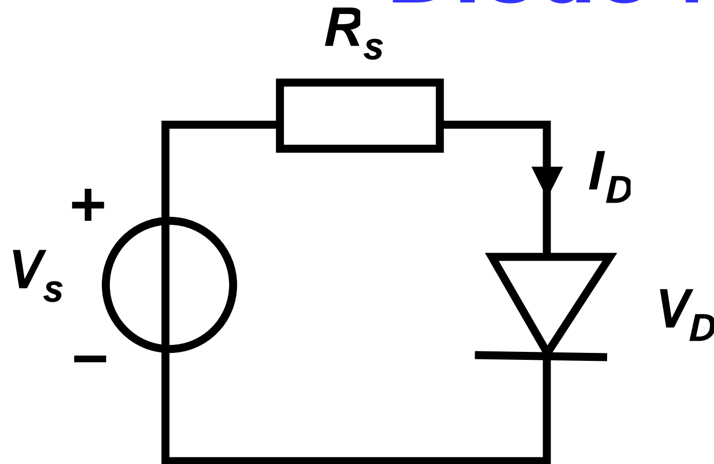




(a) Ideal diode model

(b) First-order diode model

Diode Model Example



Determine I_D

$$I_D = I_S(e^{V_D/\phi_T} - 1) \quad \text{(diode model)}$$

$$V_s - R_s I_D = V_D \quad \text{(Kirchof)}$$

$$V_s - R_s I_S(e^{V_D/\phi_T} - 1) = V_D$$ ☹

$$I_s = 0.5e^{-16} A$$

$$kT/q = 25mV$$

$$V_s = 1.6V$$

$$R_s = 1k\Omega$$

Picard Iteration

start: $V_D = 1.0V$

$$\Rightarrow I_D = (V_s - V_D)/R_S \quad = 0.600\ mA$$

$$\Rightarrow V_D = \phi_T(1 + ln(I_D/I_S)) = 0.663\ V$$

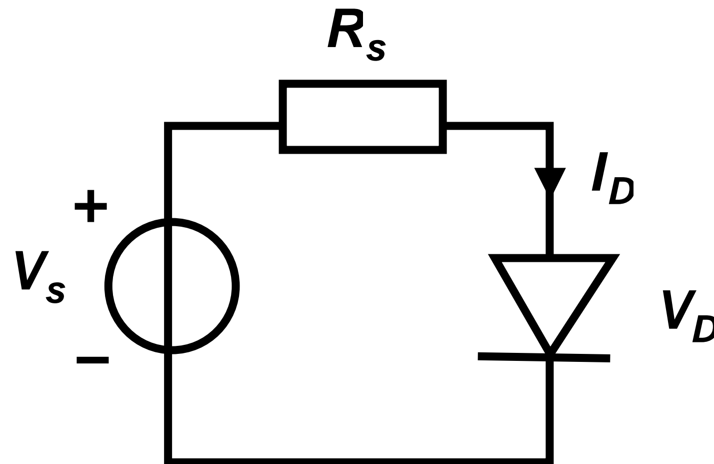
$$\Rightarrow I_D = \quad = 0.937\ mA$$

$$\Rightarrow V_D = \quad = 0.674\ V$$

$$\Rightarrow I_D = \quad = 0.926\ mA$$

$$\Rightarrow V_D = \quad = 0.674\ V$$ ☺

Diode Model Example



$I_s = 0.5e^{-16} A$

$kT/q = 25 mV$

$V_s = 1.6V$

$R_s = 1k\Omega$

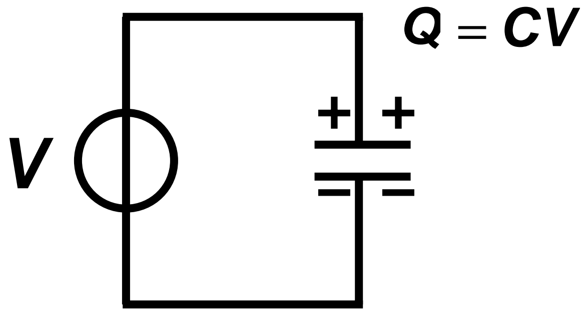
First order solution

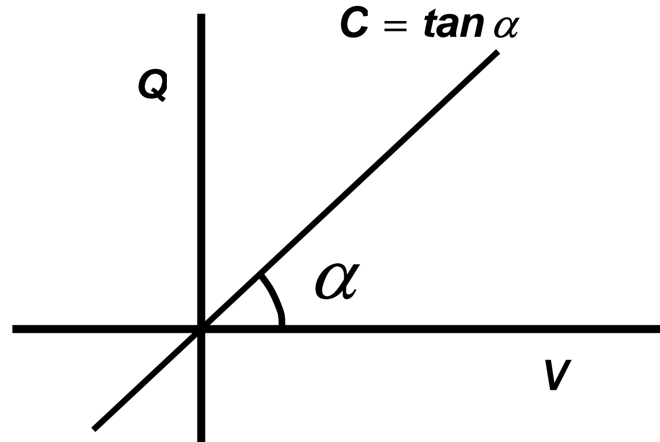
$V_D = 0.6V \quad \Rightarrow I_D = 1\,mA$ error = 8 %

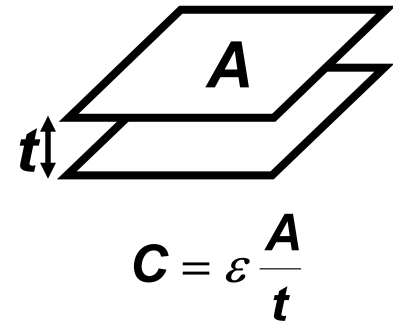
Now, take $V_s = 10.6V \quad R_s = 10K\Omega$

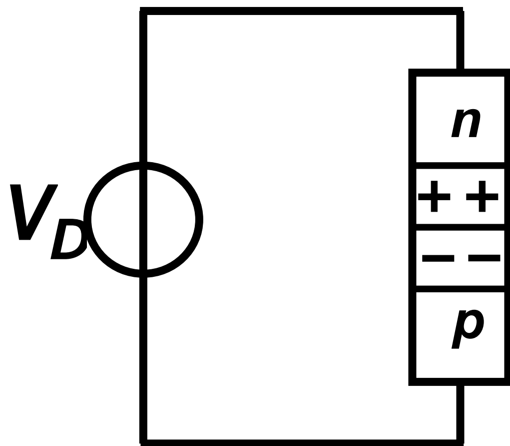
The error will be

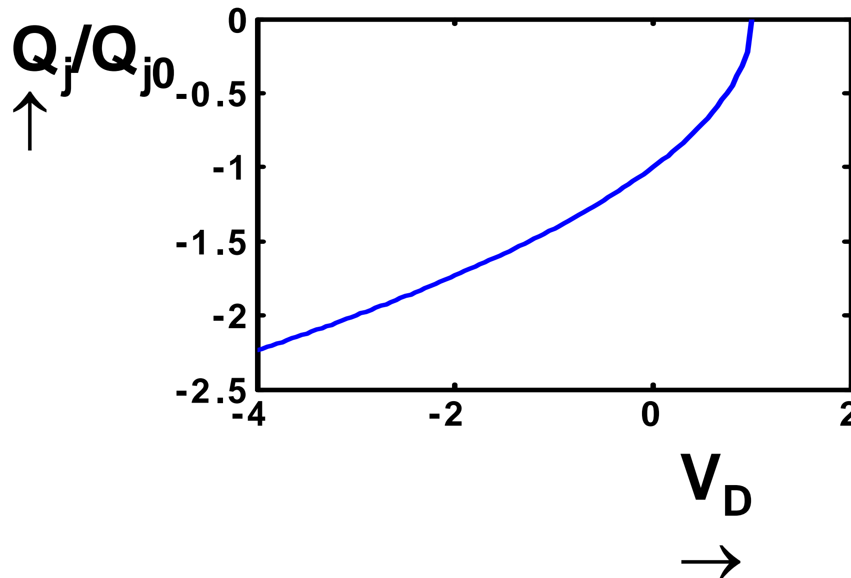
Capacitance











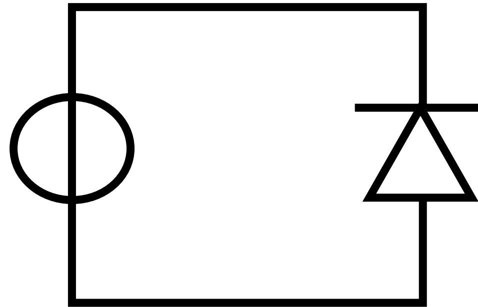
Linearized Large-Signal Diode Capacitances

Summary:

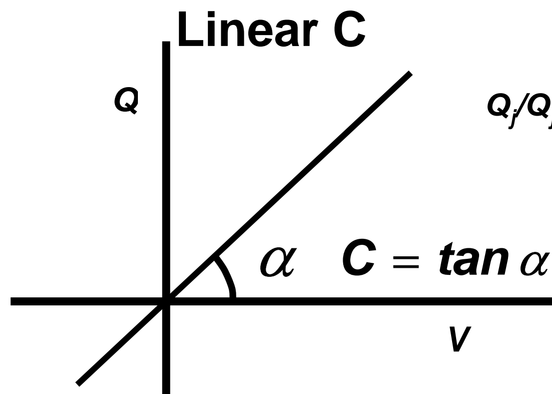
- Diode capacitances highly n…
- Difficult with manual calculatio…
- We are ultimately interested in amount … charge being stored on (or removed from) capacitor
  - Since it takes time for this to happen, this determines the final switching speed of the circuit: more charge means more time!
- Linear capacitance: $\Delta Q = C\Delta V$: easy to work with
- Small-signal capacitance: $dQ = CdV$: for analog appl.
- Non-linear capacitance: $\Delta Q = f(V_{low}, V_{high})$

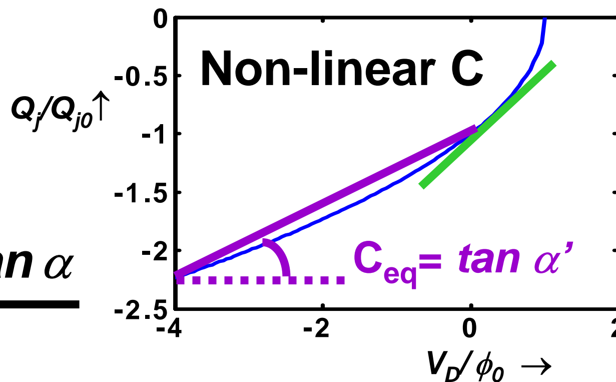
Work with C_{eq} for standardized voltage swings

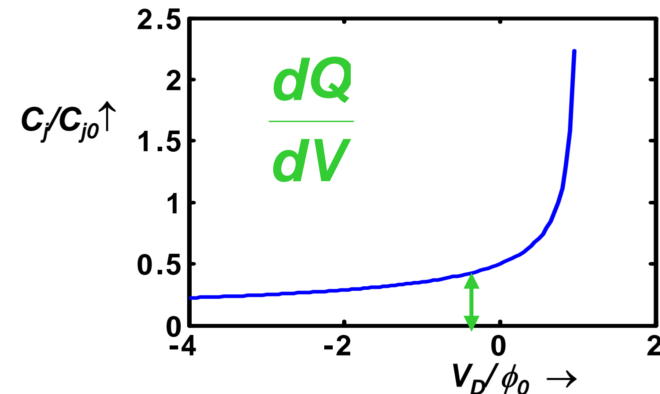
Large Signal Equivalent Diode Capacitance



$$C_{eq} = f(V_{high}, V_{low})$$
$$= \frac{Q_j(V_{high}) - Q_j(V_{low})}{V_{high} - V_{low}}$$







Linearized, large signal, depends on swing

Linearized, small signal, depends on bias

For analog applications

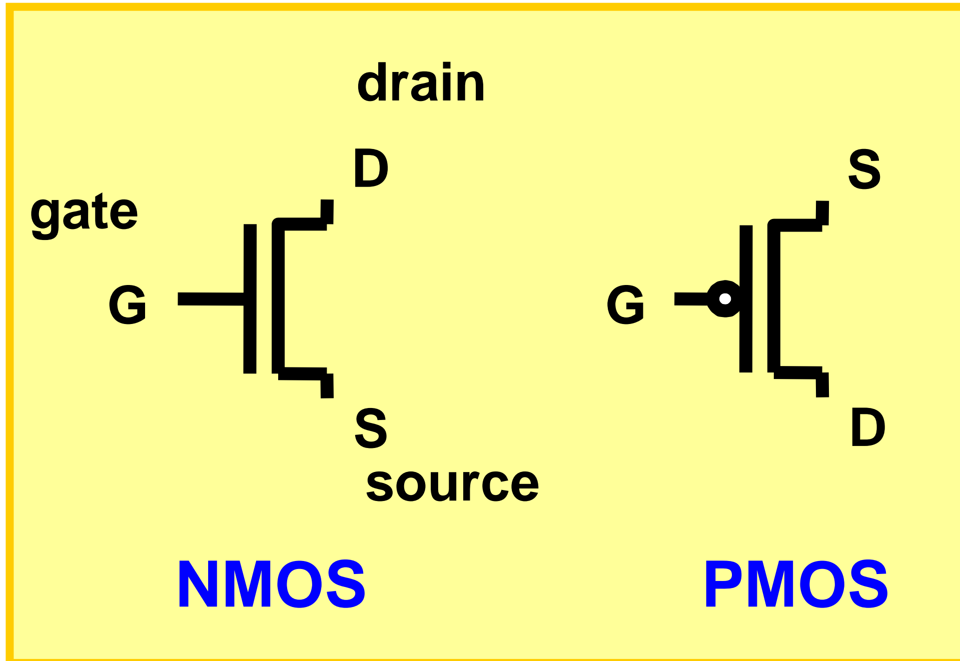
The MOS Transistor

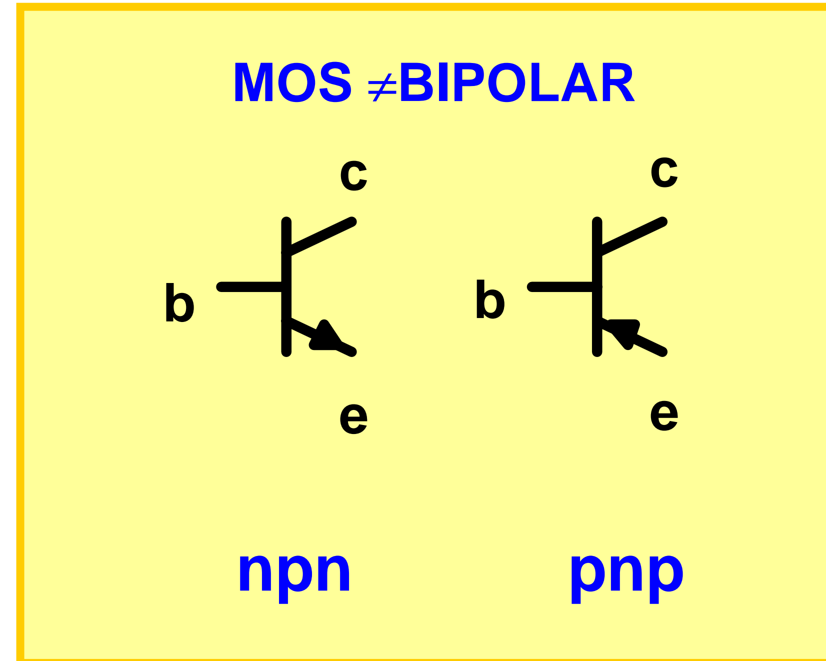
- First glance, threshold, I-V relations, models
- Dynamic behavior (capacitances), resistances, more Second-Order effects, models

The MOS Transistor – compared to Storey

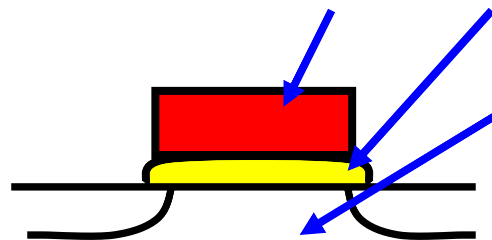
- no J-Fet
- Also other operating regions compared to saturation region (linear, velocity saturation)
- Include more effects (channel length modulation)
- Short-channel devices (bad for some analog circuits, good for (most) digital circuits)
- We will develop understanding of basic device equations

MOSFET Transistors





MOSFET = "Metal"-Oxide-Semiconductor Field-Effect Transistor



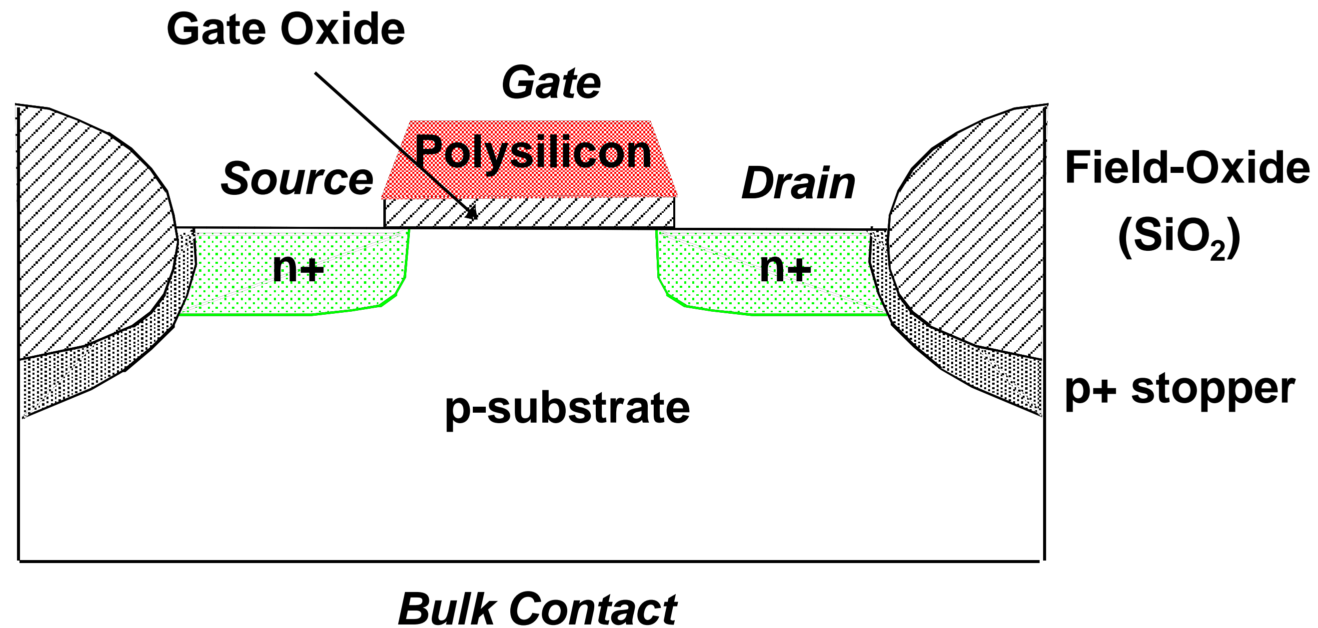
Cross-sectional view of MOSFET

Gate (terminal of MOSFET)

≠

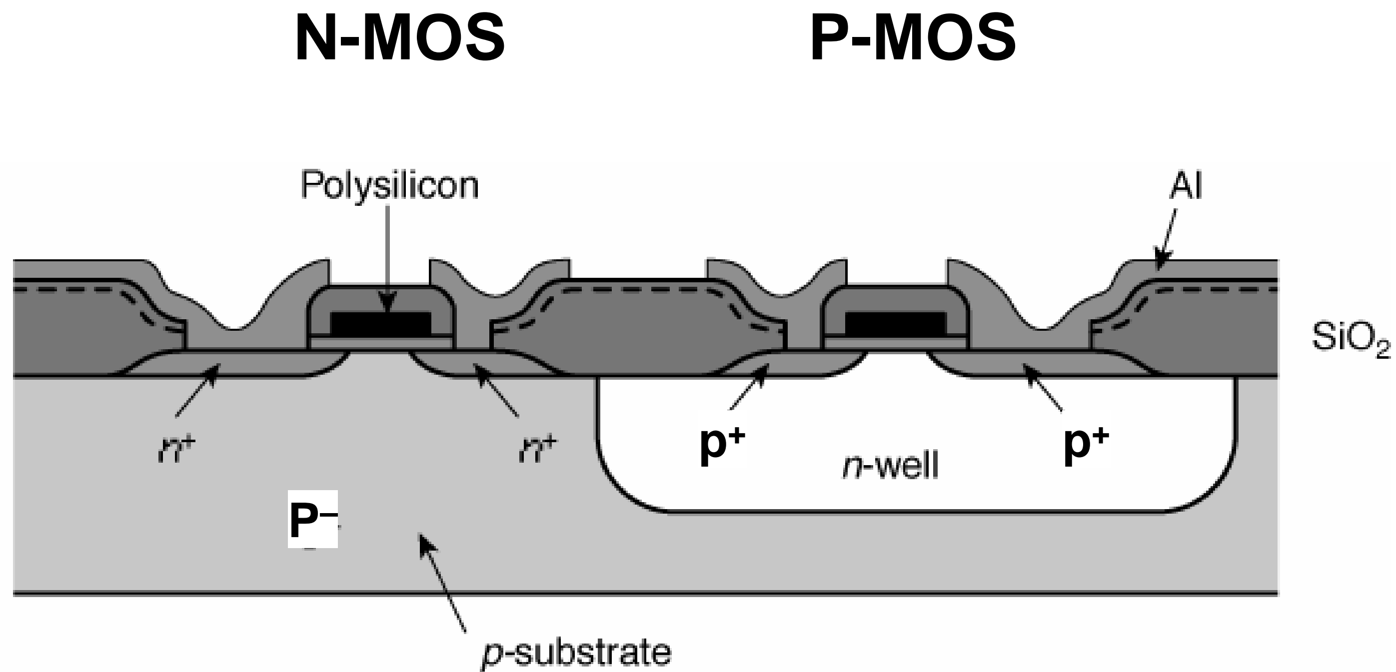
Logic gate

The MOS Transistor

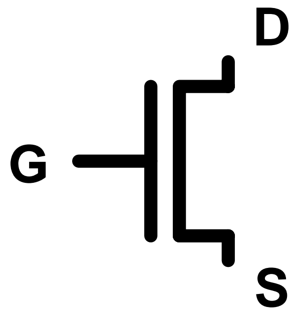


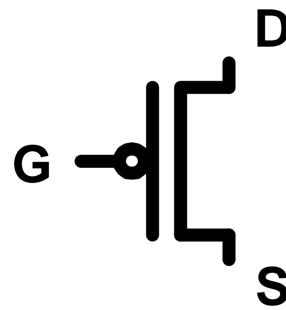
CROSS-SECTION of NMOS Transistor

Cross-Section of CMOS Technology



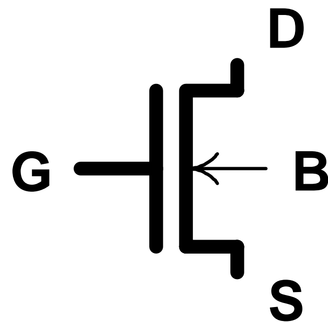
MOS Transistors

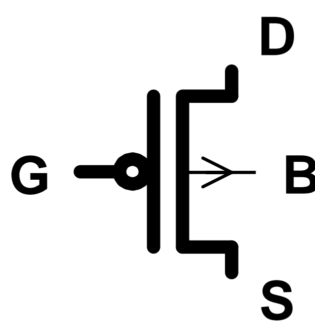




3-terminal model

bulk assumed to be connected to appropriate supply



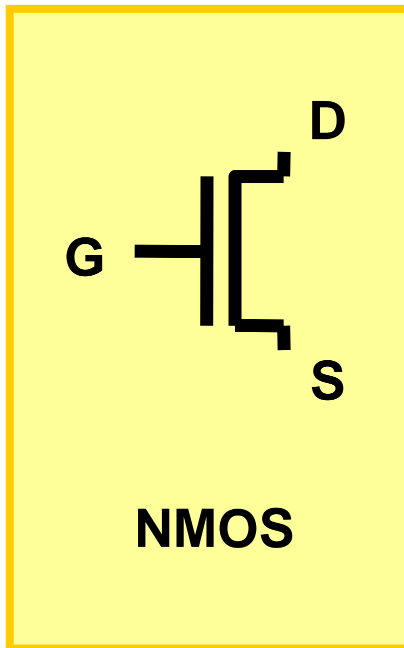


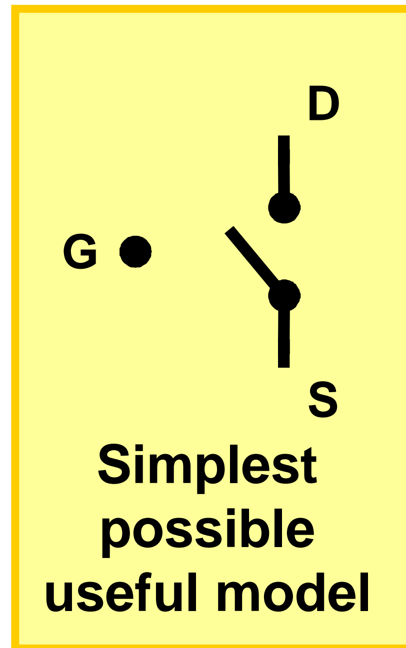
4-terminal model

B = bulk (substrate)

NMOS **PMOS**

MOS Transistor
Switch Level Models





Position of switch depends on gate voltage

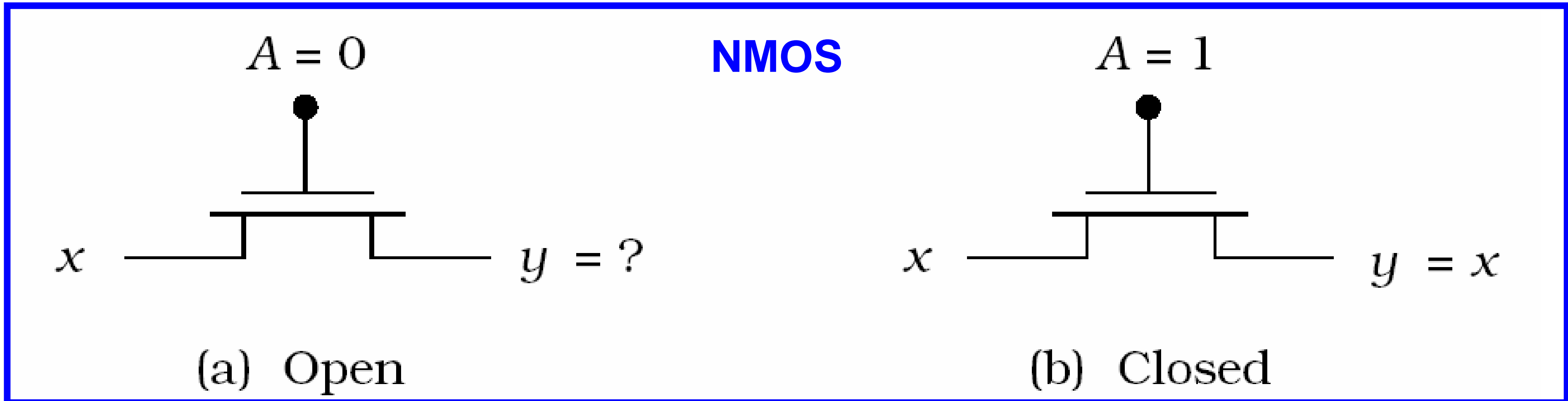
V_G	NMOS	PMOS
hi	closed	open
lo	open	closed

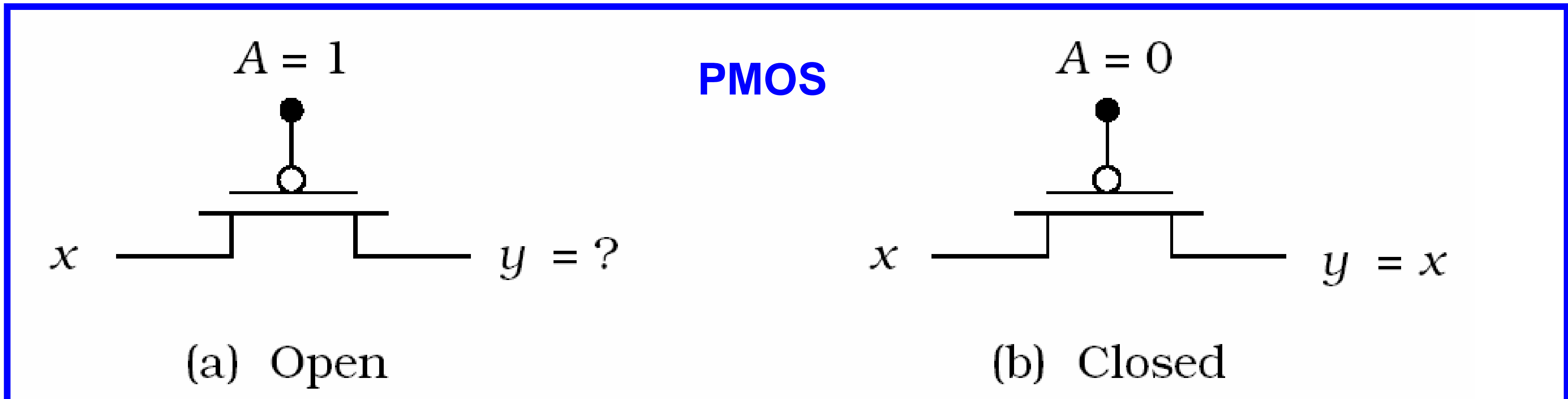
- **Connection between source and drain depends on gate voltage, current can flow from source to drain and vice versa if closed**
- **No static current flows into gate terminal**

Mos Switch Model (2)

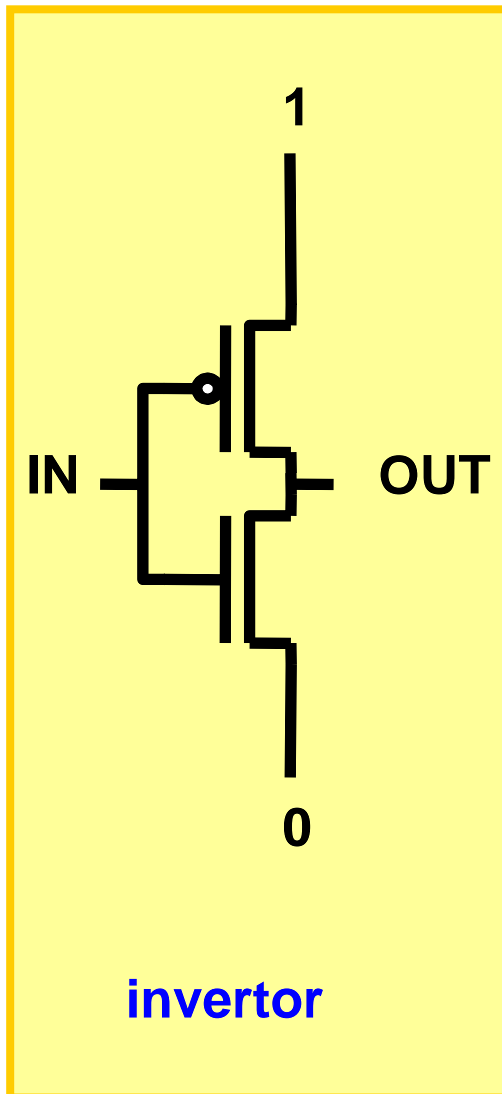
Position of switch depends on gate voltage

V_G	NMOS	PMOS
hi	closed	open
lo	open	closed

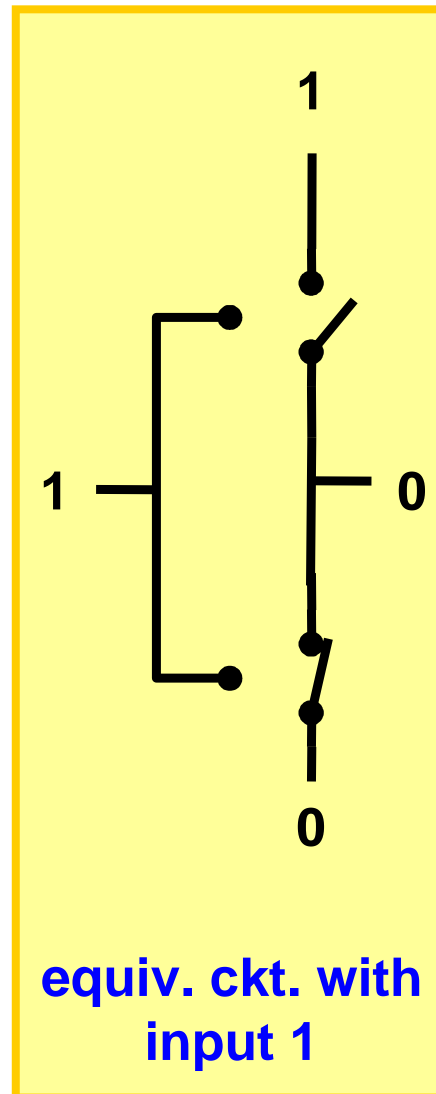




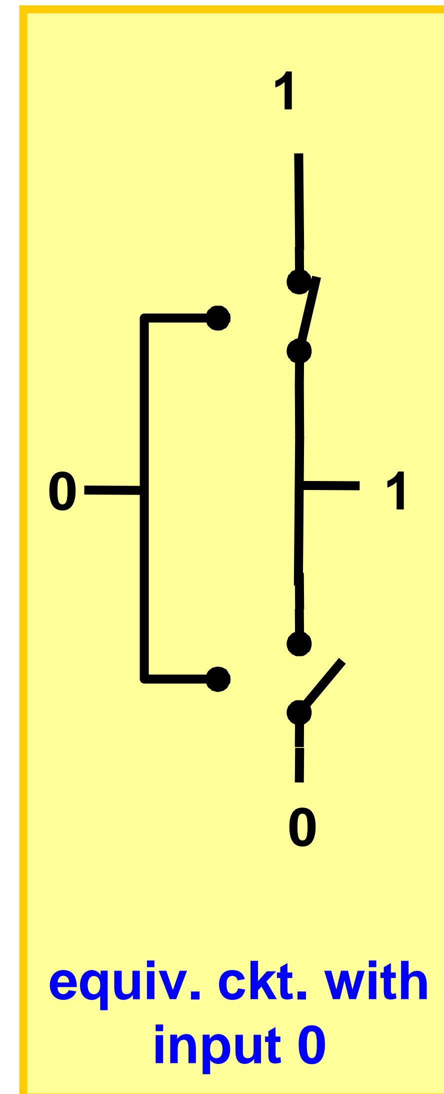
CMOS Inverter Operation Principle



invertor

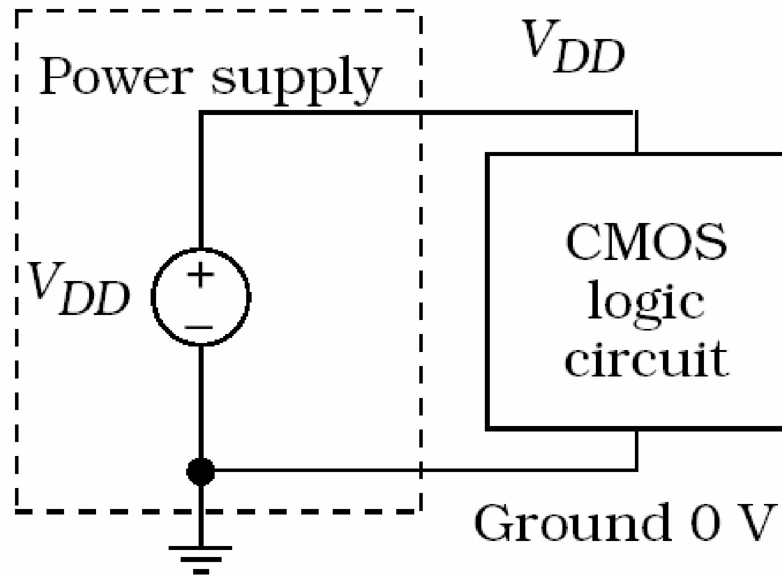


equiv. ckt. with input 1

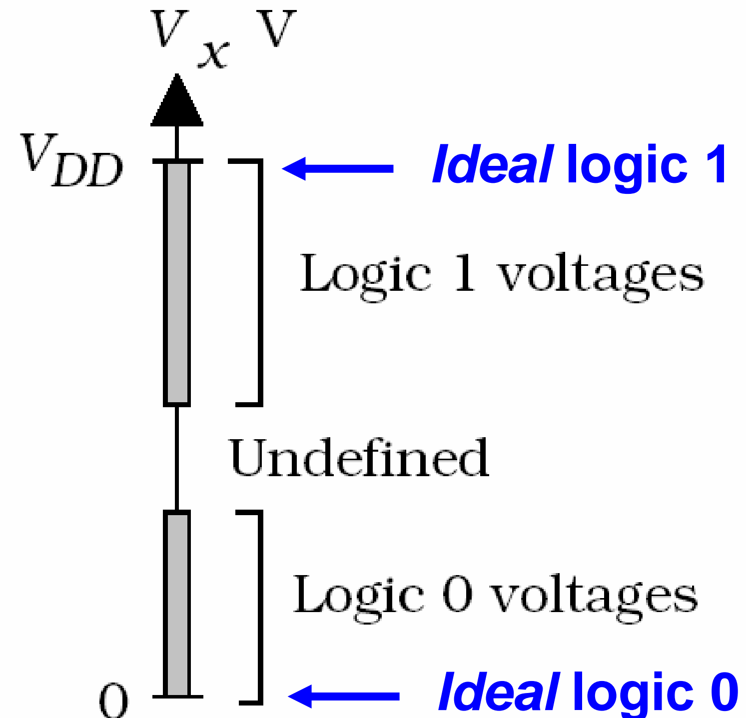


equiv. ckt. with input 0

From Logic to Voltages



(a) Power supply connection

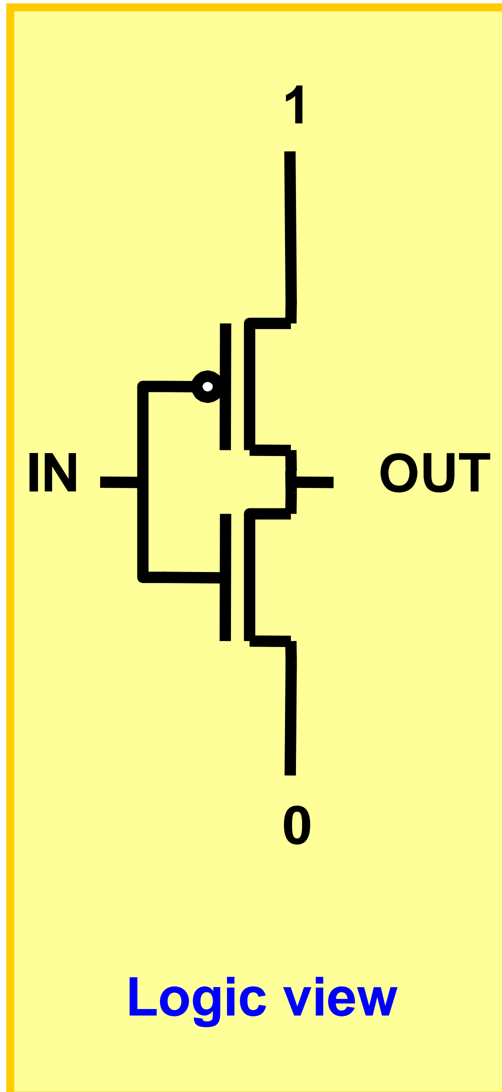


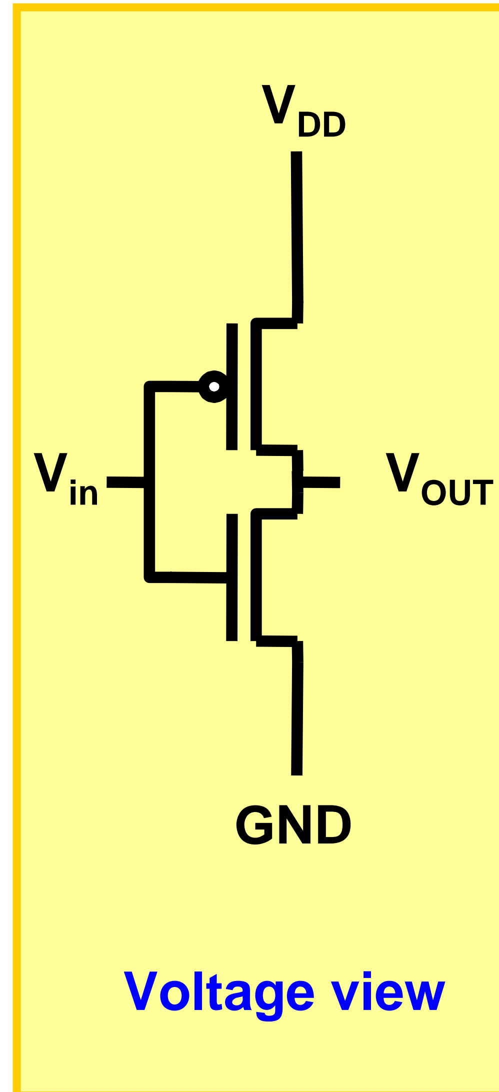
(b) Logic definitions

Ideal **logic 0 corresponds to V_x = 0V**
Ideal **logic 1 corresponds to V_x = V_{DD}**

Not all actual voltages in circuit necessarily correspond to ideal logic levels, see figure (b) above

From Logic to Voltages

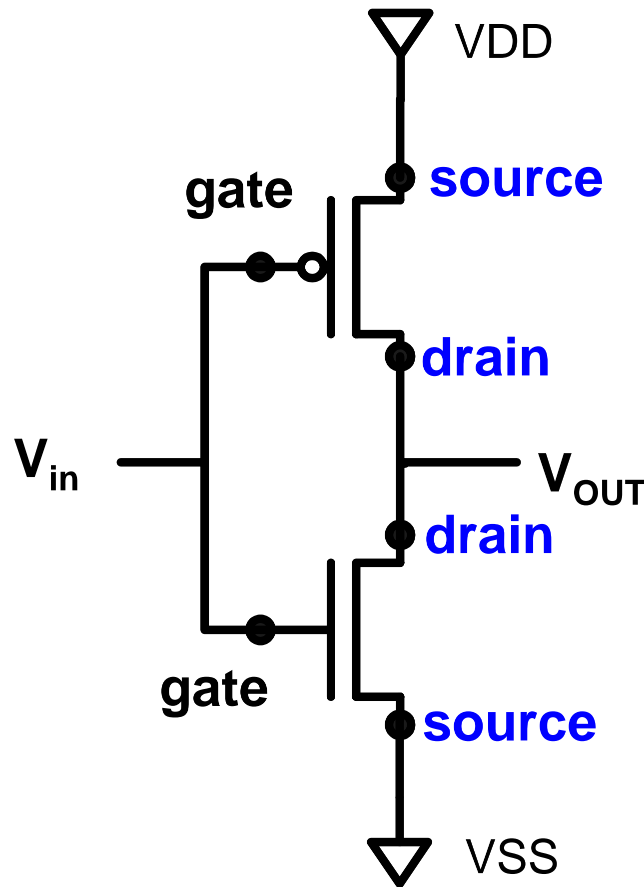




Note:

- GND = GROUND = 0V
- Sometimes also called V_{SS}
- V_{DD} is highest voltage level in circuit
- V_{DD} value depends on technology, has been reduced from 5V to 1V and lower over the years
- All voltages V_x in ckt: $0 \leq V_x \leq V_{DD}$

Source and Drain Terminals

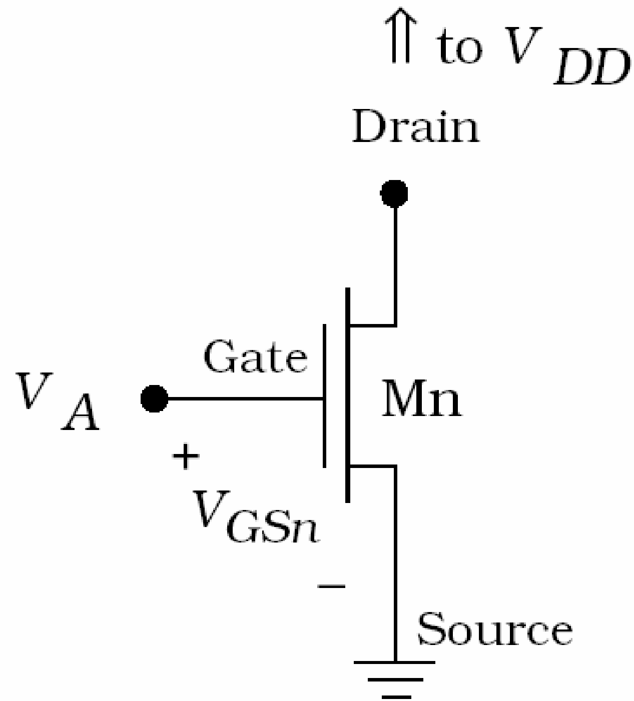


	NMOS	PMOS	PMOS
Source	Lowest potential	Highest potential	Lowest |potential|
Drain	Highest potential	Lowest potential	Highest |potential|

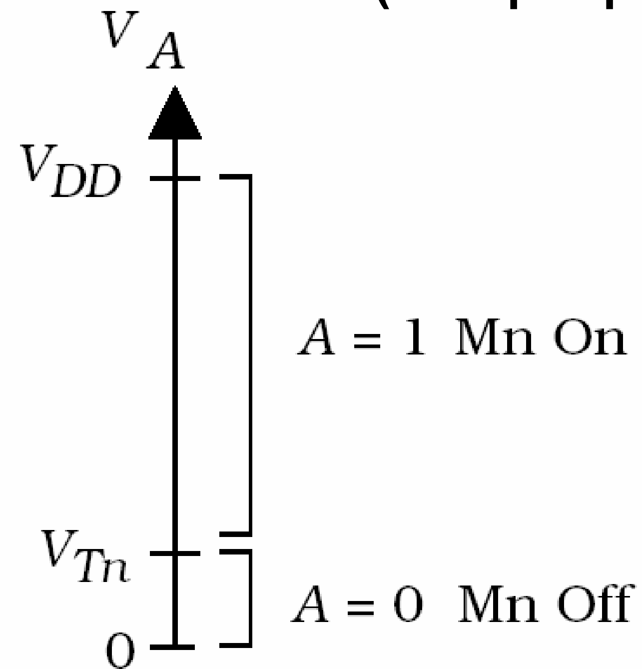
Note 1: Polarities of PMOS voltage reversed when compared to NMOS
Note 2: MOS transistor is completely symmetrical! Can interchange source and drain, without any effect. Source/drain is only a naming convention.

nFET Threshold Voltage

(drempelspanning)



(a) Gate-source voltage

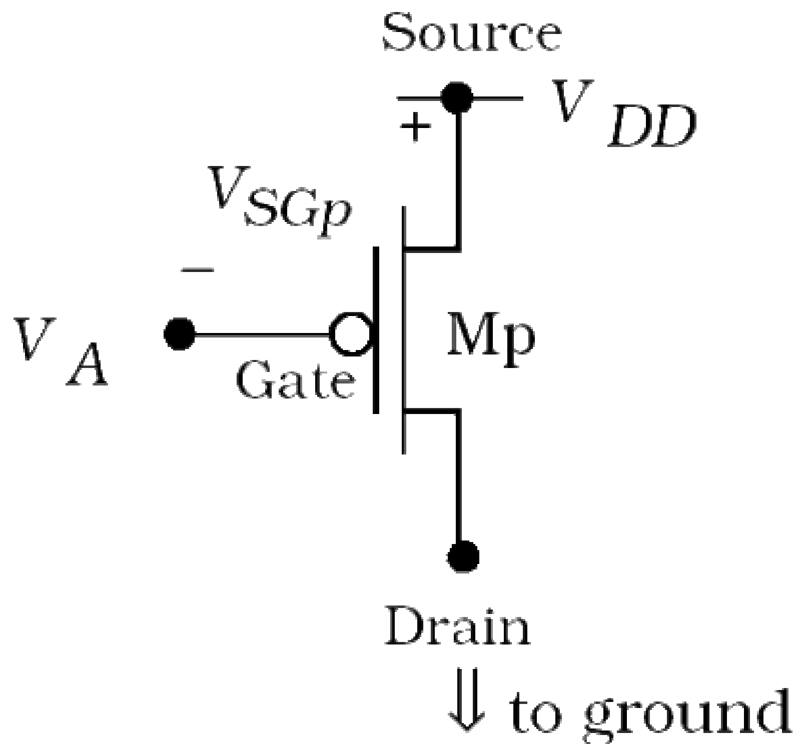


(b) Logic translation

nFET is off when $V_{GSn} \leq V_{Tn}$
nFET is on when $V_{GSn} > V_{Tn}$

V_{Tn} ~ 0.5 … 0.7V

pFET Threshold Voltage



nFET is off when $V_{GSn} \leq V_{Tn}$
nFET is on when $V_{GSn} > V_{Tn}$

pFET and nFET behave **complementary**

V_{Tp} ~ –0.5 … –0.7V (negative!)

Equivalent conditions

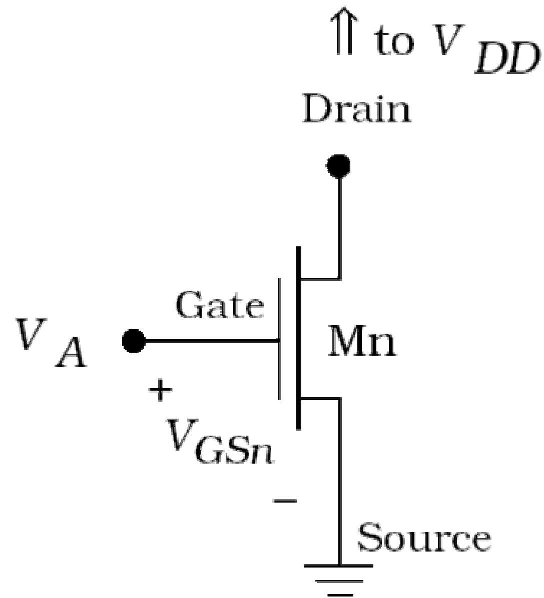
pFET is off when $V_{GSp} \geq V_{Tp}$
pFET is on when $V_{GSp} < V_{Tp}$

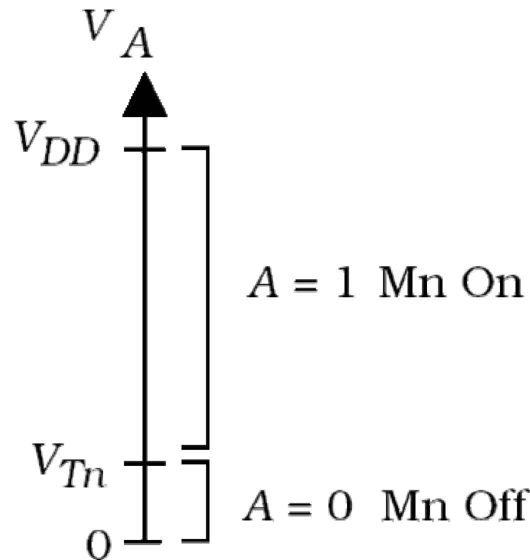
pFET is off when $-V_{GSp} \leq -V_{Tp}$
pFET is on when $-V_{GSp} > -V_{Tp}$

pFET is off when $|V_{GSp}| \leq |V_{Tp}|$
pFET is on when $|V_{GSp}| > |V_{Tp}|$

Often most useful

Excercise

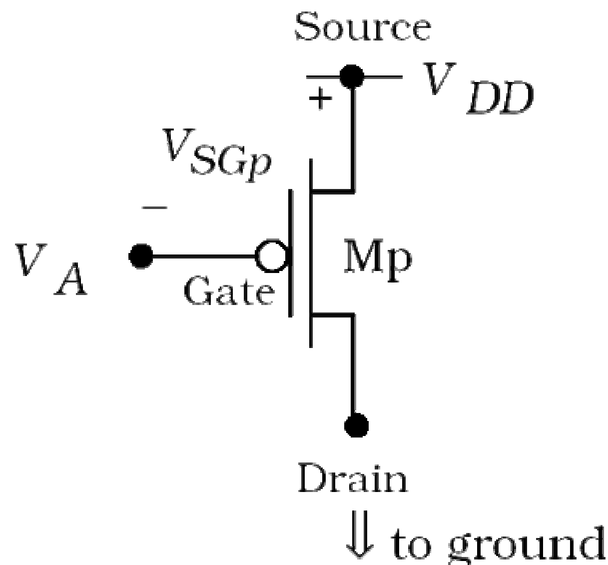




transistor on the left using

nFET is off when $V_{GSn} \leq V_{Tn}$
nFET is on when $V_{GSn} > V_{Tn}$

corresponds to diagram on right

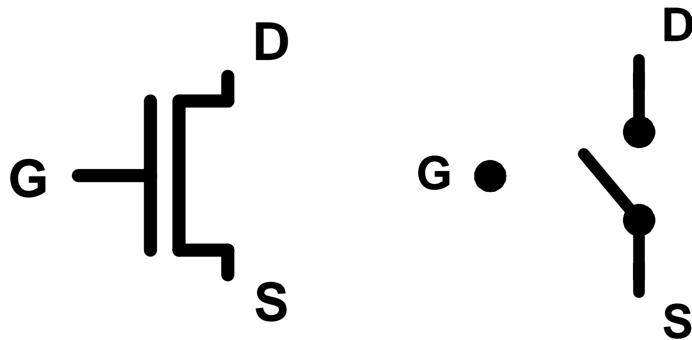


Draw same diagram for PMOS using

pFET is off when $-V_{GSp} \leq -V_{Tp}$
pFET is on when $-V_{GSp} > -V_{Tp}$

MOS Transistor Treshold Voltage

Treshold voltage V_T: point at which transistor turns on



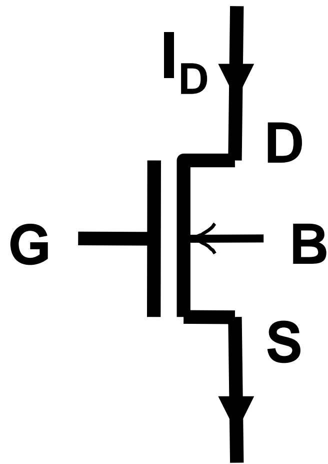
Position of switch depends on gate voltage (relative to source)

V_{GS}	NMOS	PMOS
$V_{GS}>V_T$	closed	open
$V_{GS}<V_T$	open	closed

Is this all there is?

- You don't believe that (CMOS) life can be so simple, do you?
- Discuss some of the things that you would expect to be non-idealities of CMOS as a switch
- Since we want to design CMOS circuits, we need a deeper understanding of CMOS circuits
- Next slide shows where we are going

MOS Models for Manual Analysis



determined by circuit

V_{DS}, V_{GS}, V_{SB}

determined by technology

$k, \lambda, V_{DSAT}, V_{T0}, \gamma, \phi_F$

MOS model for manual analysis

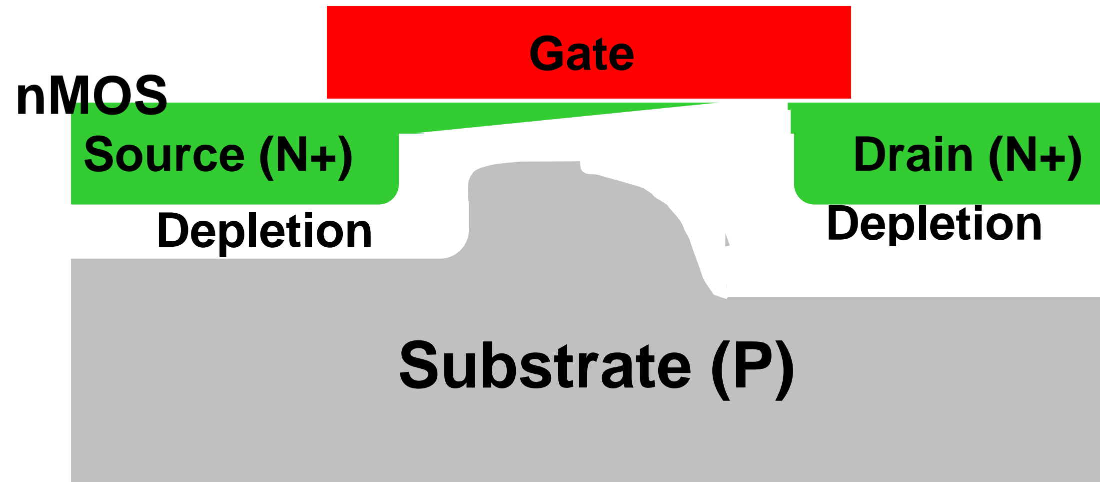
$$I_D = k\left(V_{GT}V_{MIN} - 0.5V_{MIN}^2\right)\left(1 + \lambda V_{DS}\right) \qquad \text{for } V_{GT} \geq 0$$

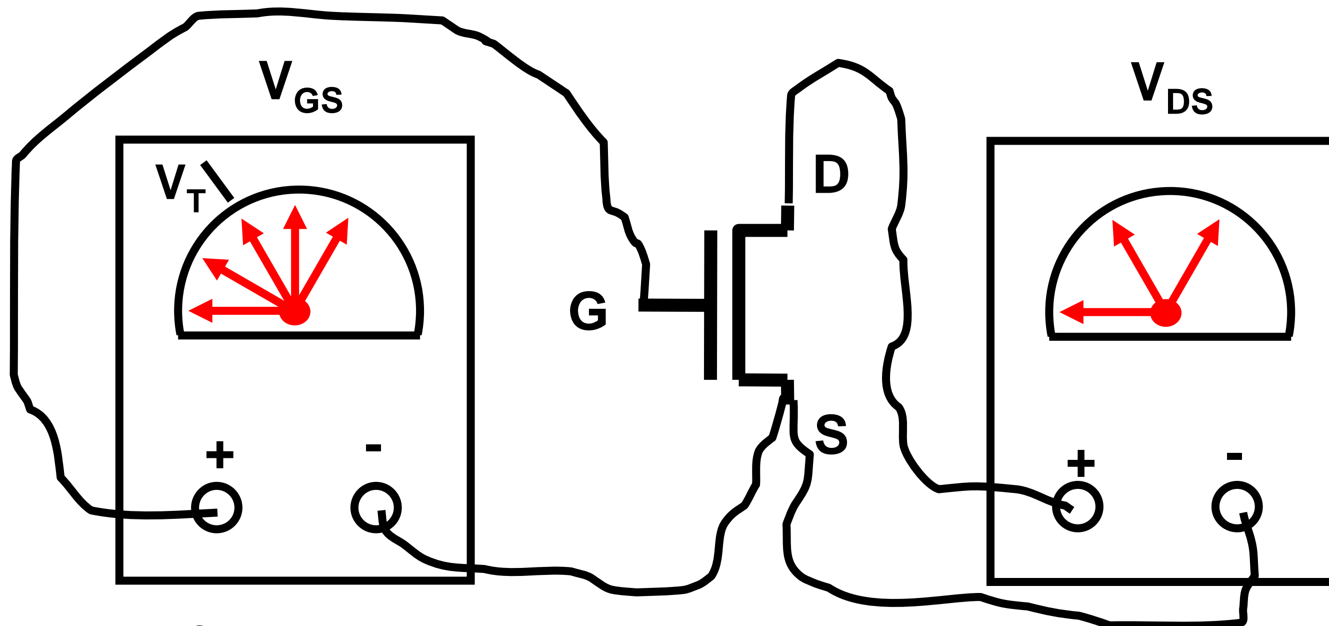
$$= 0 \qquad \text{for } V_{GT} \leq 0$$

$$V_{MIN} = MIN\left(V_{DS}, V_{GT}, V_{DSAT}\right)$$

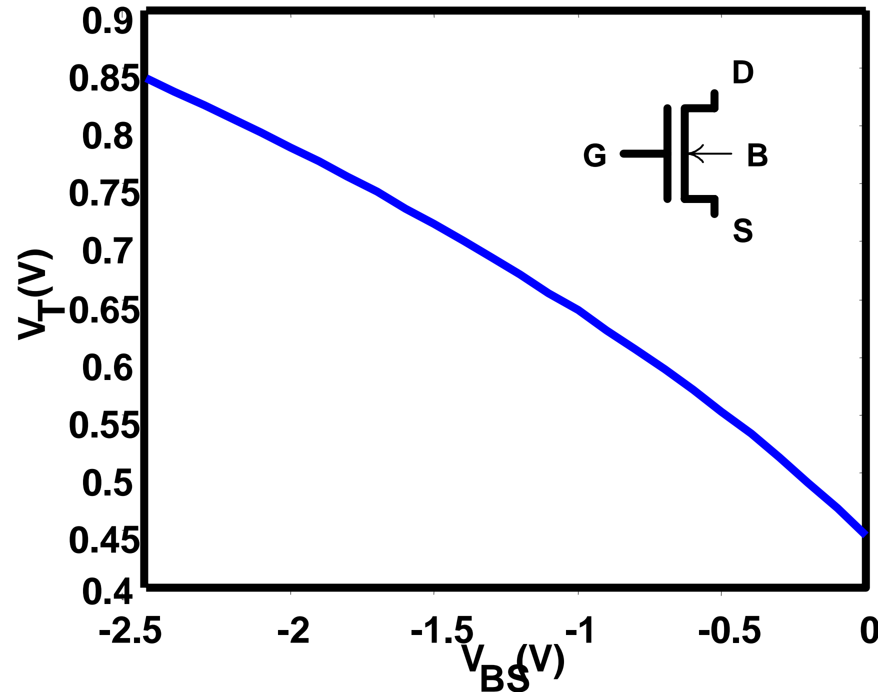
$$V_{GT} = V_{GS} - V_T, \qquad V_T = V_{T0} + \gamma\left(\sqrt{\left|-2\phi_F + V_{SB}\right|} - \sqrt{\left|-2\phi_F\right|}\right)$$

nMOS Transistor Operation





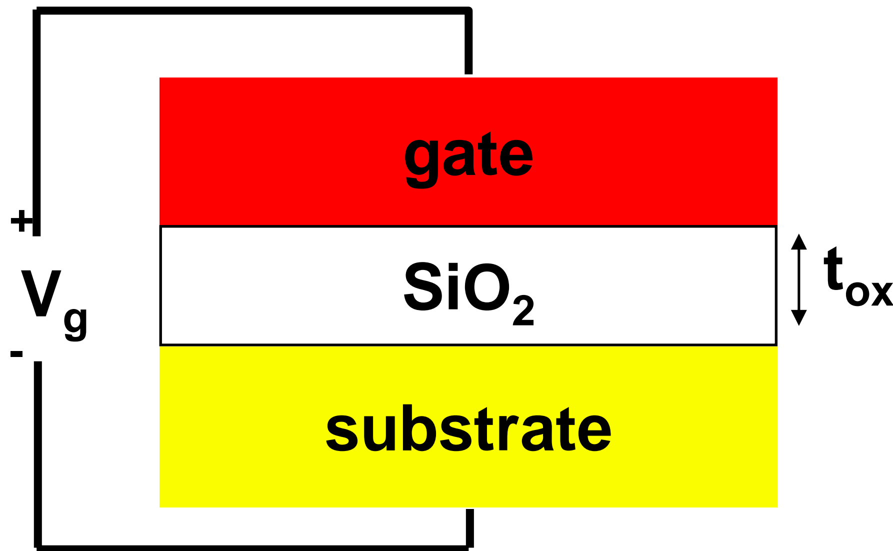
Body Effect



- V_T is not constant
- Depends on V_S vs V_B
- Our wish is to understand & predict behavior of CMOS devices
- We will start with V_T

MOSFET gate as capacitor

- **Gate capacitance helps determine charge in channel which forms inversion region.**
- **Basic structure of gate is parallel-plate capacitor:**



$$C_{ox} = \varepsilon_{ox} / t_{ox}$$

$$\varepsilon_{ox} = \varepsilon_0 \varepsilon_r$$

$$\varepsilon_0 = 8.85 \times 10^{-12} \text{ F/m}$$

$$\varepsilon_r = 3.9 \quad (SiO_2)$$

Note: [F] vs. [F/m²]

The Threshold Voltage

$$V_T = \phi_{ms} - 2\phi_F - \frac{Q_B}{C_{ox}} - \frac{Q_{SS}}{C_{ox}} - \frac{Q_I}{C_{ox}}$$

Contact Potential
Fermi Potential
Depletion Layer Charge
Surface Charge
Implants

$$Q_B = \gamma(\sqrt{|-2\phi_F + V_{SB}|})$$

with

$$\gamma = \frac{\sqrt{2q\varepsilon_{SI}N_A}}{C_{ox}}$$

Body Effect Coefficient

Forget all this

$$V_T = V_{T0} + \gamma(\sqrt{|-2\phi_F + V_{SB}|} - \sqrt{|-2\phi_F|})$$

But be able to use this

with

$$V_{T0} = \phi_{ms} - 2\phi_F - \frac{Q_{B0}}{C_{ox}} - \frac{Q_{SS}}{C_{ox}} - \frac{Q_I}{C_{ox}}$$

and this

$I_D(V_{GS}, V_{DS}, V_{BS})$

MOS model for manual analysis

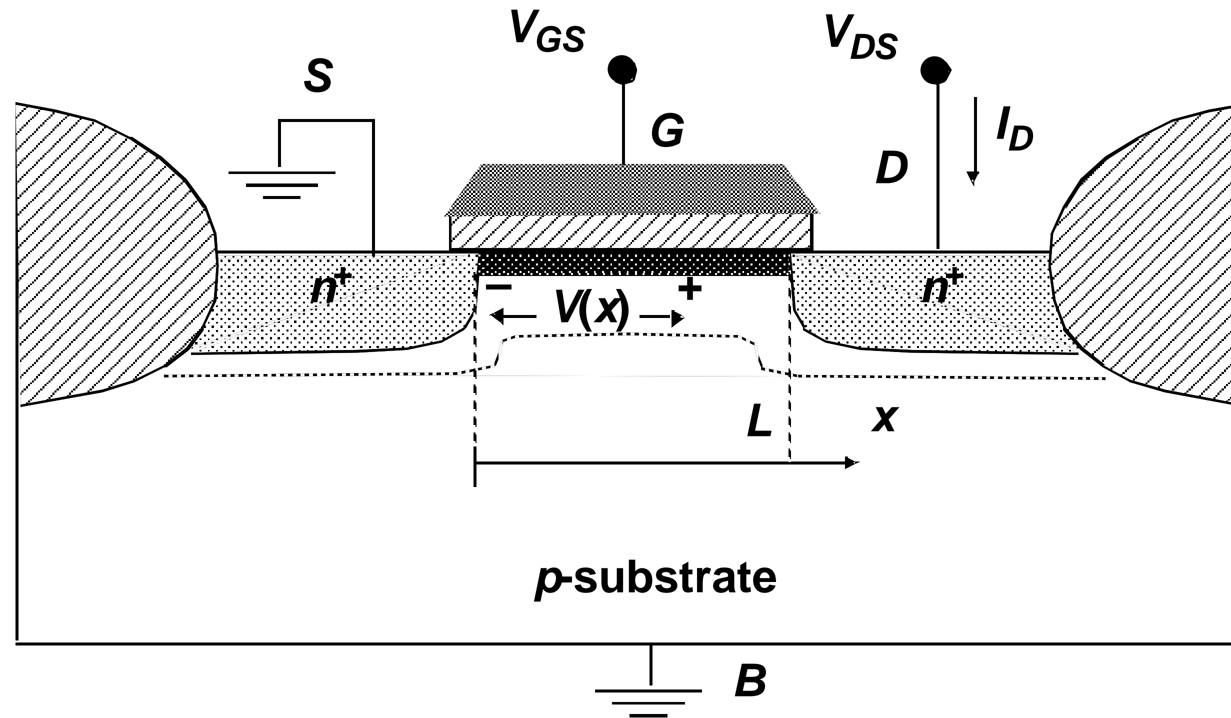
$$I_D = k\left(V_{GT}V_{MIN} - 0.5V_{MIN}^2\right)\left(1+\lambda V_{DS}\right) \qquad \text{for } V_{GT} \geq 0$$

$$= 0 \qquad \text{for } V_{GT} \leq 0$$

$$V_{MIN} = MIN\left(V_{DS}, V_{GT}, V_{DSAT}\right)$$

- Different operation regions
- Different behavior for each region:
  - off
  - resistive ← NEXT
  - saturation
  - velocity saturation

Current-Voltage Relations



MOS transistor and its bias conditions

I-V In Resistive Region

$$C_{ox} = \frac{\varepsilon_{ox}}{t_{ox}}$$

$$Q_i(x) = -C_{ox}[V_{GS} - V(x) - V_T]$$ **Inversion Charge**

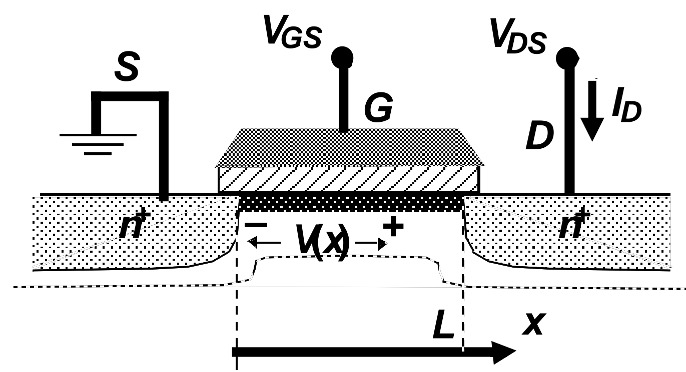
$$I_D = -\mu_n \frac{dV}{dx} Q_i(x) W$$

I_D **Drain Current**

μ_n **mobility (n-Si)**

$$\int_0^L I \;\ldots\; V]\,dV$$

$$v_n = -\mu_n \varepsilon(x) = \mu_n \frac{dV}{dx}$$



$$I_D L = \mu_n C_{ox} W \left[(V_{GS} - V_T)V - \frac{1}{2}V^2 \right]_0^{V_{DS}}$$

$$I_D = \mu_n C_{ox} \frac{W}{L} \left[(V_{GS} - V_T)V_{DS} - \frac{1}{2}V_{DS}^2 \right]$$

Process Gain and Device Gain

$$I_D = \mu_n C_{ox} \frac{W}{L}\left[(V_{GS} - V_T)V_{DS} - \frac{1}{2}V_{DS}^2\right]$$

$$k_n' = \mu_n C_{ox} = \mu_n \frac{\varepsilon_{ox}}{t_{ox}}$$

Process transconductance parameter

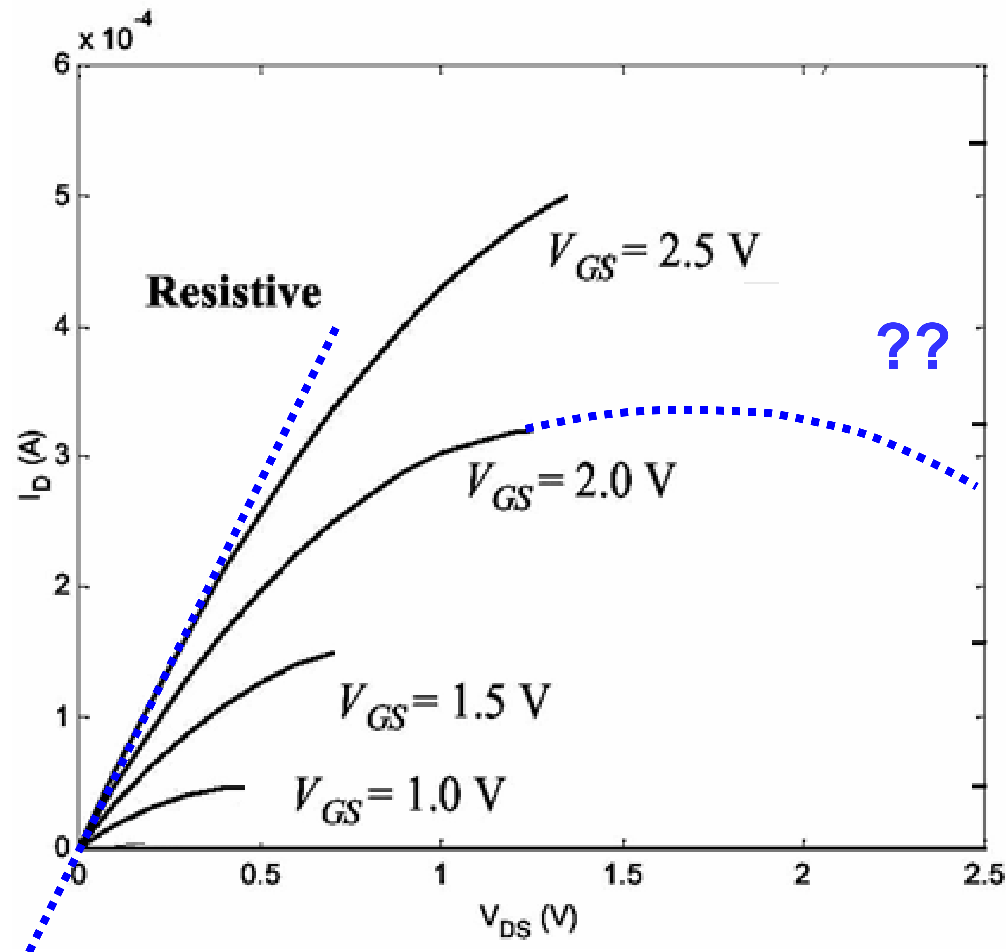
$$k = k_n' \frac{W}{L}$$

Gain factor of device

$$I_D = k\left[(V_{GS} - V_T)V_{DS} - \frac{1}{2}V_{DS}^2\right]$$

(resistive/linear/ohmic regime)

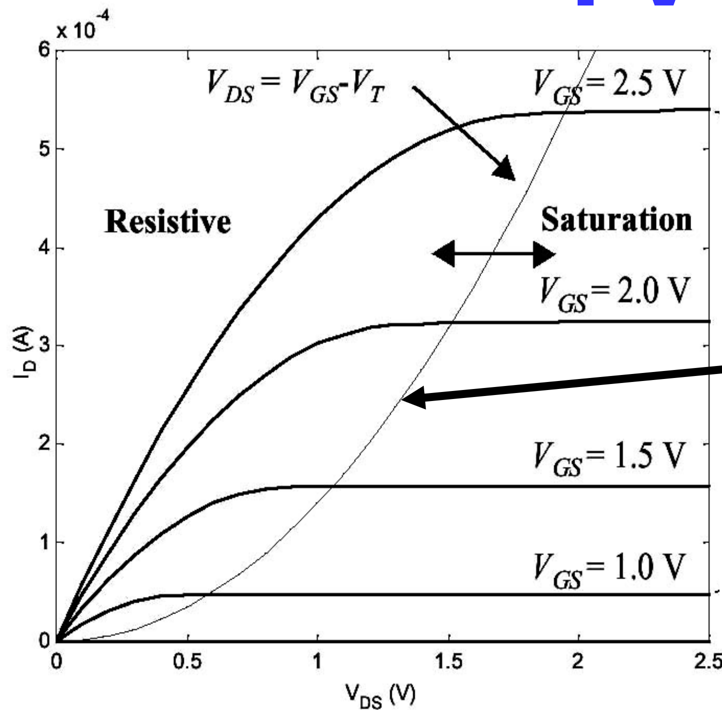
I-V Relation



- **No!**

$$I_D = k\left[(V_{GS} - V_T)V_{DS} - \frac{1}{2}V_{DS}^2\right]$$ **(resistive regime)**

I-V Relation



This curve is where I_D curves begin to run flat: I_D does not anymore depend on V_{DS}

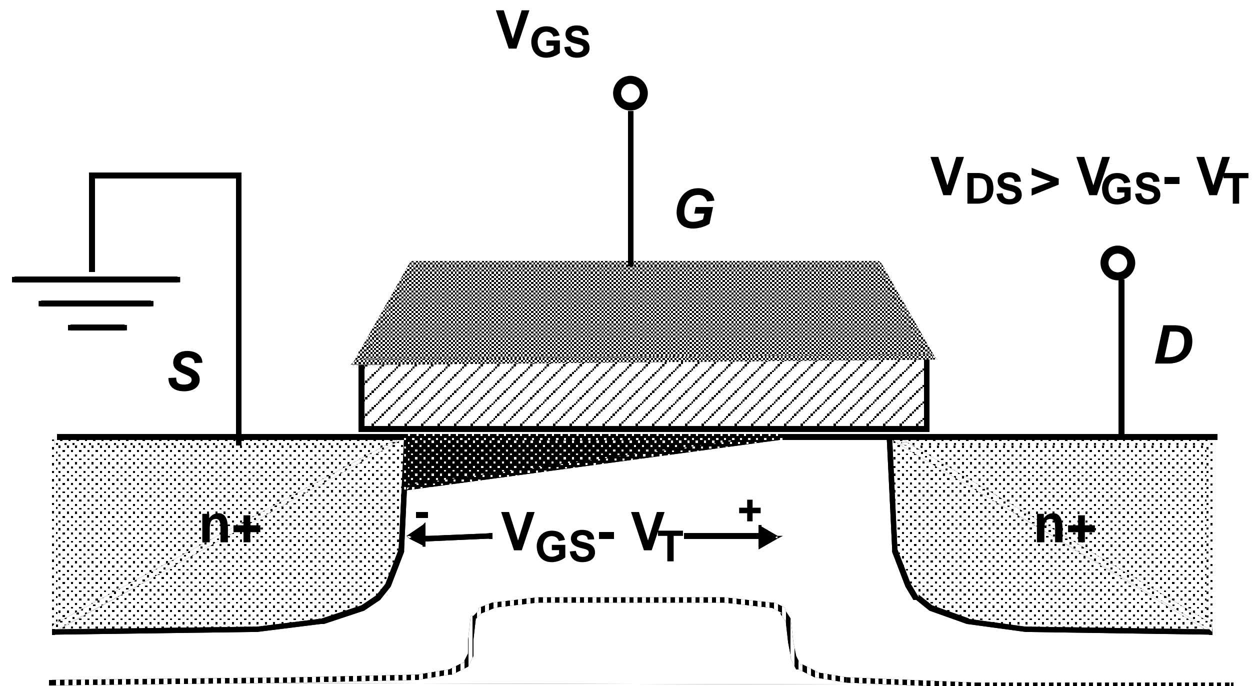
$$I_D = k\left[(V_{GS} - V_T)V_{DS} - \frac{1}{2}V_{DS}^2\right]$$

The curve is given by

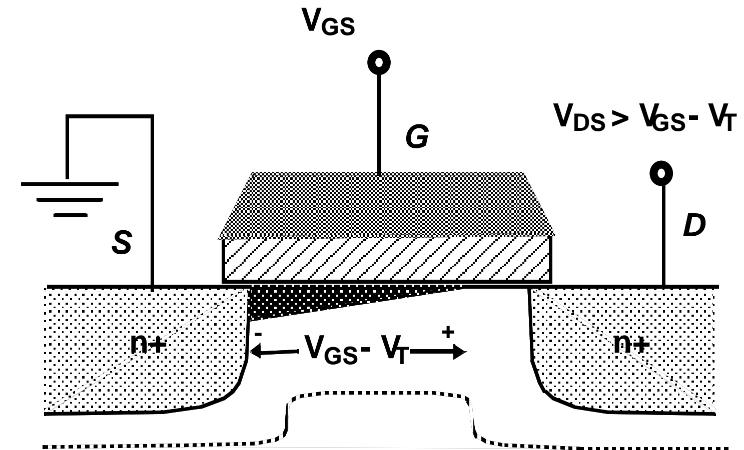
$$\frac{dI_D}{dV_{DS}} = k\left[(V_{GS} - V_T) - V_{DS}\right] = 0 \Rightarrow V_{DS} = V_{GS} - V_T$$

The value $V_{DS} = V_{GS}-V_T$ is special: it is the boundary between resistive regime and saturation regime (pinch-off)

Transistor in Saturation



I-V in saturation



$V_{DS} < V_{GS}-V_T$:

$$I_D = k\left[(V_{GS}-V_T)V_{DS} - \frac{1}{2}V_{DS}^2\right]$$

Saturation: $V_{DS} > V_{GS}-V_T$

Current does not increase when $V_{DS} > V_{GS} - V_T$

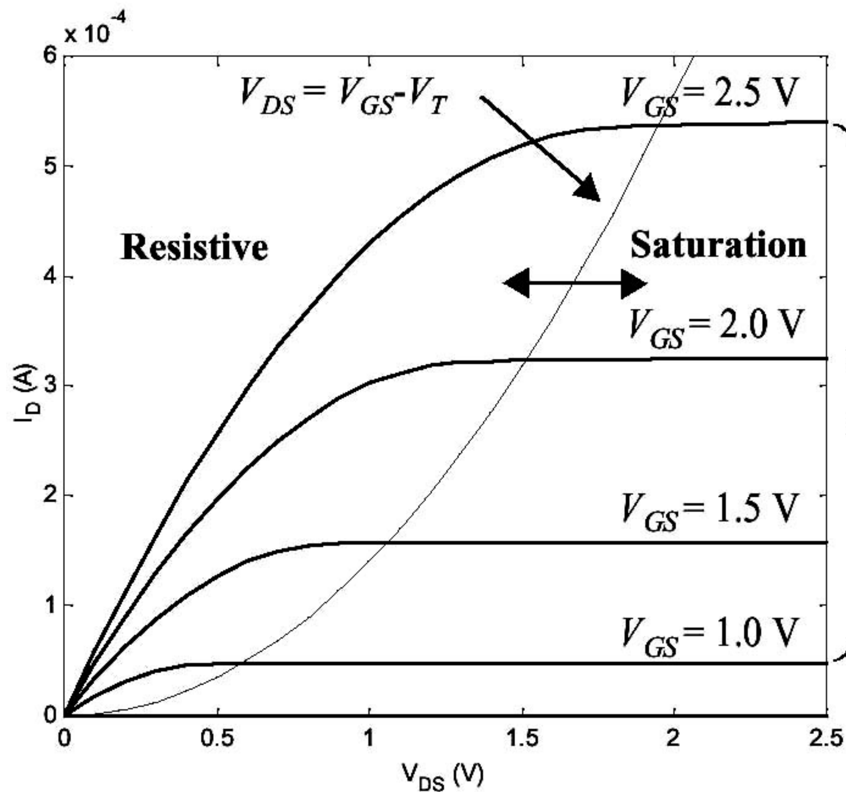
$$I_{DSAT} = I_D\Big|_{V_{DS} = V_{GS} - V_T}$$

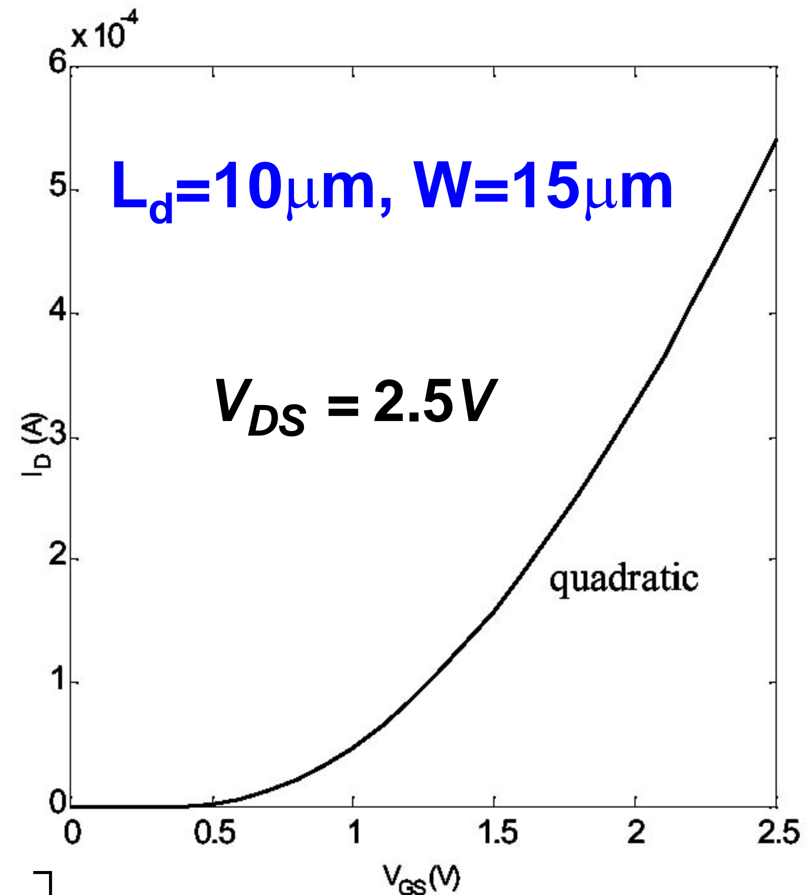
Saturation current

$$I_{DSAT} = k\left[(V_{GS}-V_T)(V_{GS}-V_T) - \frac{1}{2}(V_{GS}-V_T)^2\right]$$

$$= \frac{1}{2}k(V_{GS}-V_T)^2$$

I-V Relation

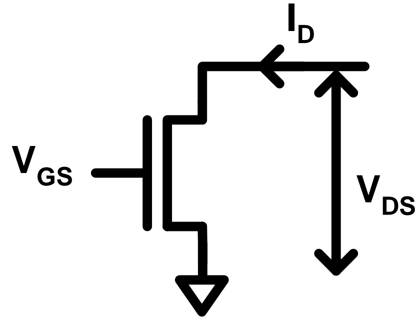




$$I_D = k\left[(V_{GS} - V_T)V_{DS} - \frac{1}{2}V_{DS}^2\right]$$ (resistive regime)

$$= \frac{1}{2}k(V_{GS} - V_T)^2$$ (saturation)

Output Impedance



Definition: $$Z_{out} = \frac{dV_{ds}}{dI_d}$$

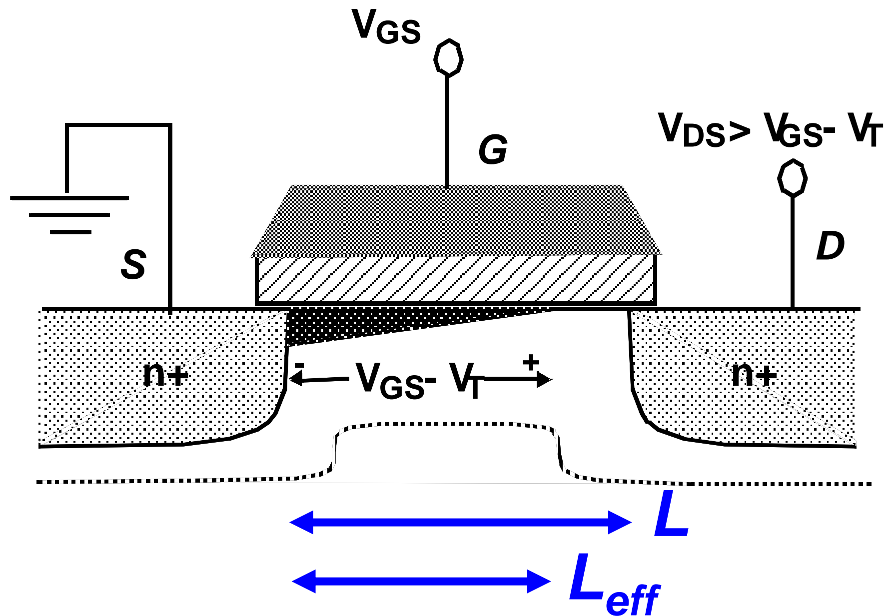
$$I_D = \frac{1}{2}k(V_{GS} - V_T)^2$$

What is the output impedance?

Is this plausible?

What is happening?

Channel Length Modulation



Empirical Model for Effective Channel Length

$$L_{eff} = \frac{L}{1 + \lambda V_{DS}}$$

$$I_{DSAT} = \frac{1}{2} k_n' \frac{W}{L_{eff}} (V_{GS} - V_T)^2$$

$$= \frac{1}{2} k_n' \frac{W}{L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$$

$$= \frac{1}{2} k (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$$

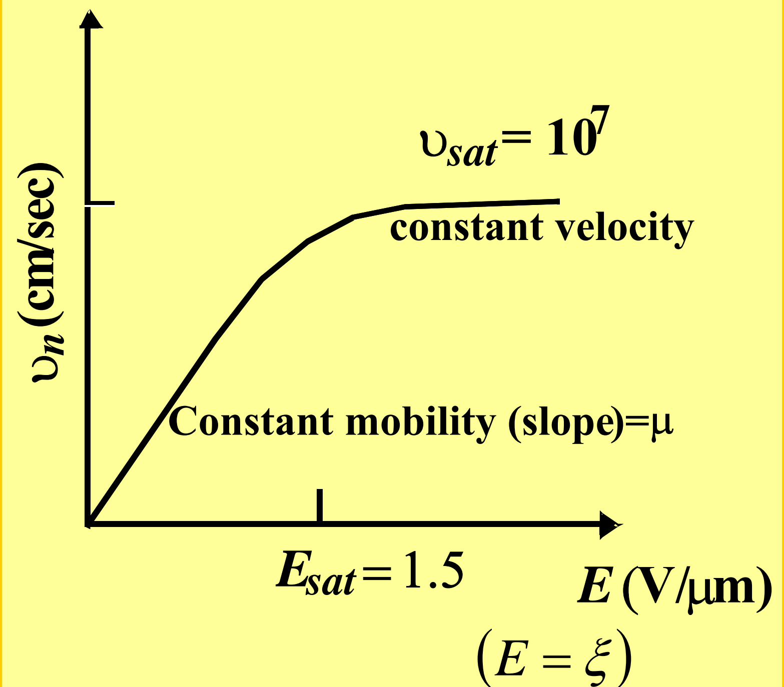
Velocity Saturation (1)

1. Still model not complete: need to include effects of limited carrier velocity

2. Carrier velocity (ideal model):
Linear with field

$$v_n = -\mu_n \xi(x) = \mu_n \frac{dV}{dx}$$

3. Reality



4. Simple v_{sat} Model:

$$v_n = \mu_n \xi \qquad \text{for } \xi \le \xi_c$$

$$= \mu_n \xi_c = v_{sat} \qquad \text{for } \xi \ge \xi_c$$

ξ_c Critical Field

v_{sat} Saturation *Velocity*

Velocity Saturation (2)

Onset of velocity saturation can be translated into a critical voltage V_{DS}: V_{DSAT}. This value depends on L.

Velocity saturation parameters

$$V_{DSAT} = L\xi_c = \frac{Lv_{sat}}{\mu_n}$$

voltage

velocity

L	V_{DSAT}
2	3
1	1.5
0.25	0.375
0.18	0.27
…	…

First order, empirical model

$$I_{DSAT} = I_D(V_{DS} = V_{DSAT})$$

$$= k\left[(V_{GS} - V_T)V_{DSAT} - \frac{1}{2}V_{DSAT}^2\right]$$

Velocity Saturation

Overview

$$I_D = k\left[(V_{GS} - V_T)V_{DS} - \frac{1}{2}V_{DS}^2\right]$$

resistive regime
base equation

$$= \frac{1}{2}k(V_{GS} - V_T)^2$$

saturation: $V_{DS} \rightarrow V_{GS}-V_T$

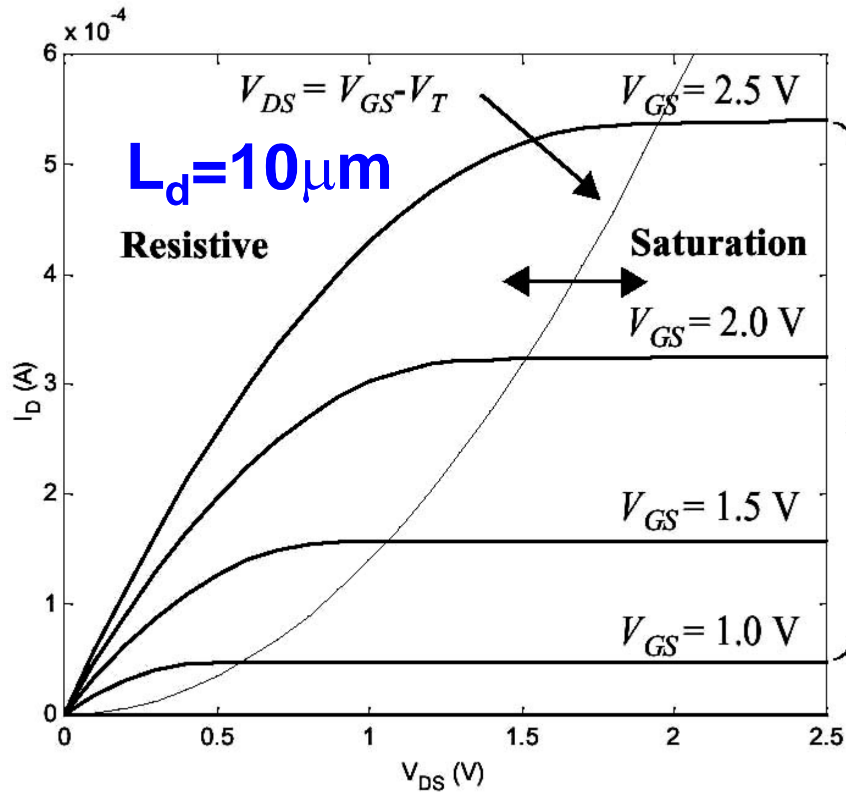
$$= k\left[(V_{GS} - V_T)V_{DSAT} - \frac{1}{2}V_{DSAT}^2\right]$$

velocity sat: $V_{DS} \rightarrow V_{DSAT}$

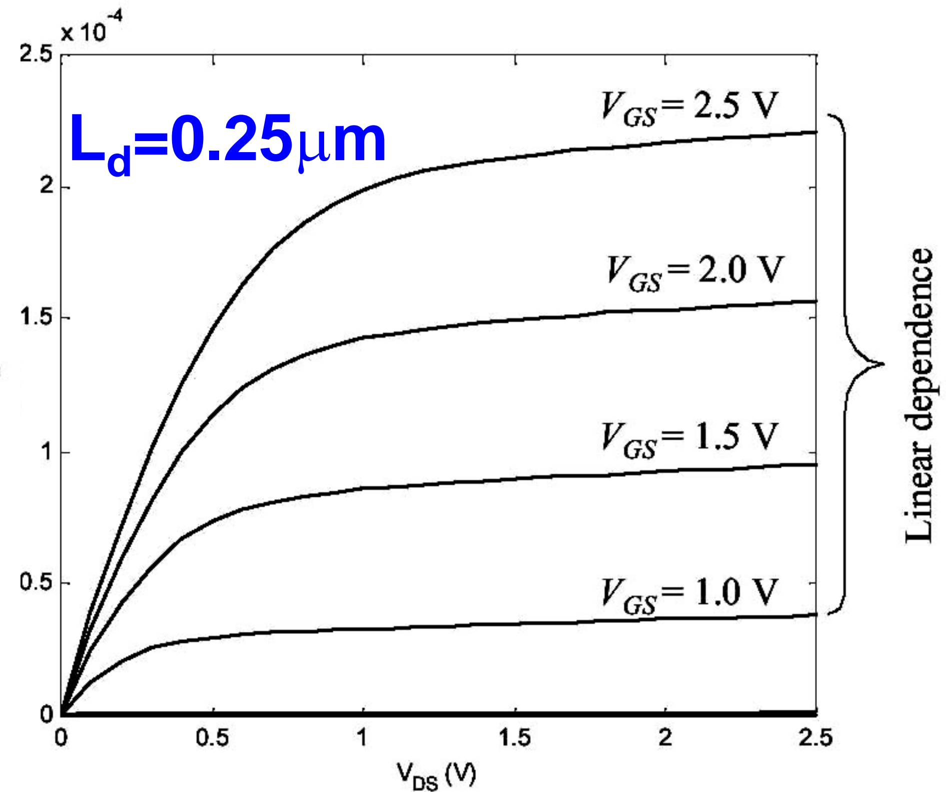
$$I_D = I'_D(1 + \lambda V_{DS})$$

Channel Length Modulation

I_D as a function of V_{DS}



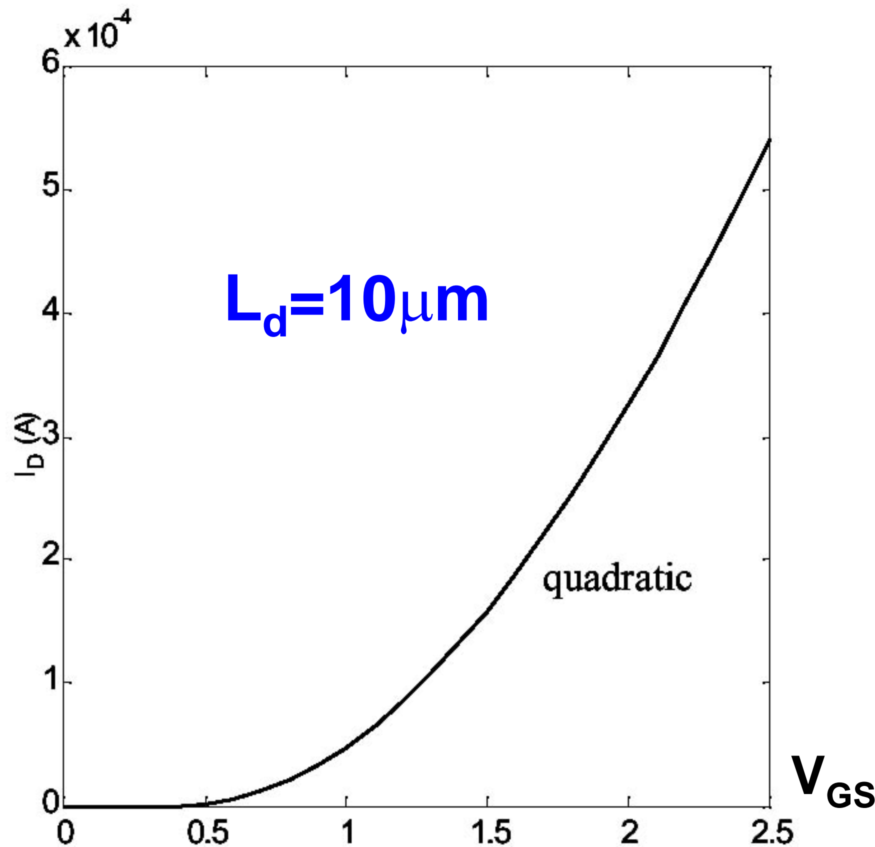
Long channel device w/o velocity saturation



Short channel device with velocity saturation

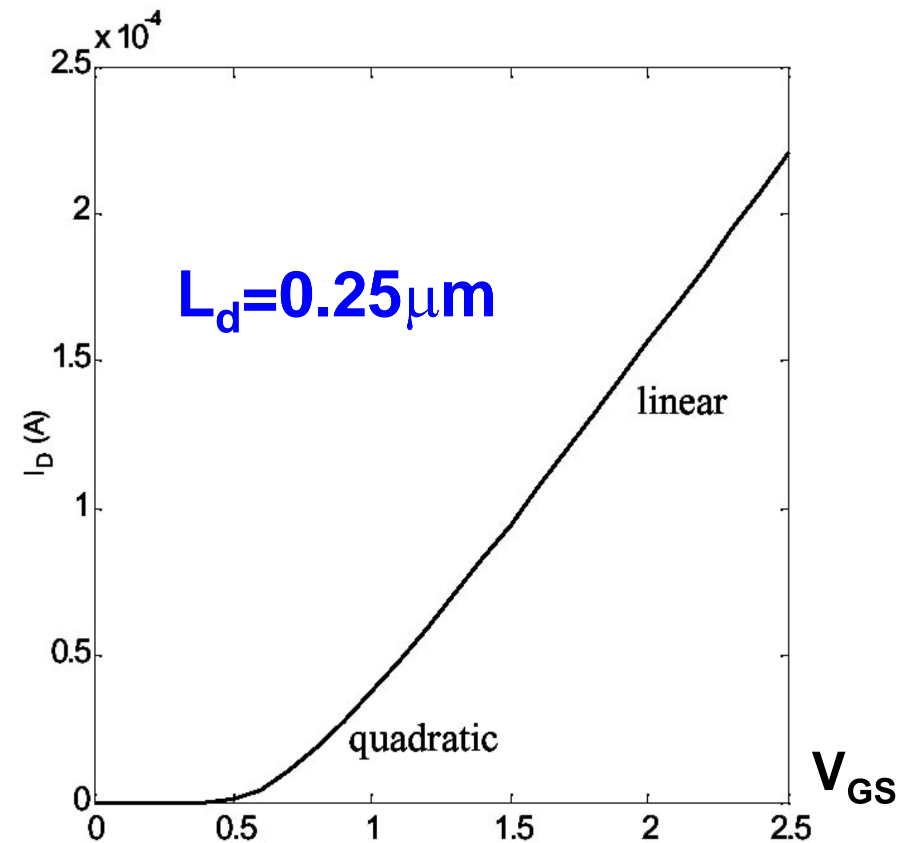
$$W = 1.5L$$

I_D as a function of V_{GS}



Long channel device w/o velocity saturation

$$I_D = \frac{1}{2}k(V_{GS} - V_T)^2$$



Short channel device with velocity saturation

$$I_D = k\left[(V_{GS} - V_T)V_{DSAT} - 0.5V_{DSAT}^2\right]$$

MOS Models for Manual Analysis

Region Specific Models

Channel length modulation added to resitive region, in order to enforce continuity

$$I'_D = k\left(V_{GT}V_{DS} - 0.5V_{DS}^2\right)$$ Resistive region

$$I'_D = k\left(V_{GT}V_{GT} - 0.5V_{GT}^2\right)$$ Saturation

$$I'_D = k\left(V_{GT}V_{DSAT} - 0.5V_{DSAT}^2\right)$$ Velocity Saturation

$$I_D = I'_D(1 + \lambda V_{DS})$$ Channel Length Modulation

Comprehensive model

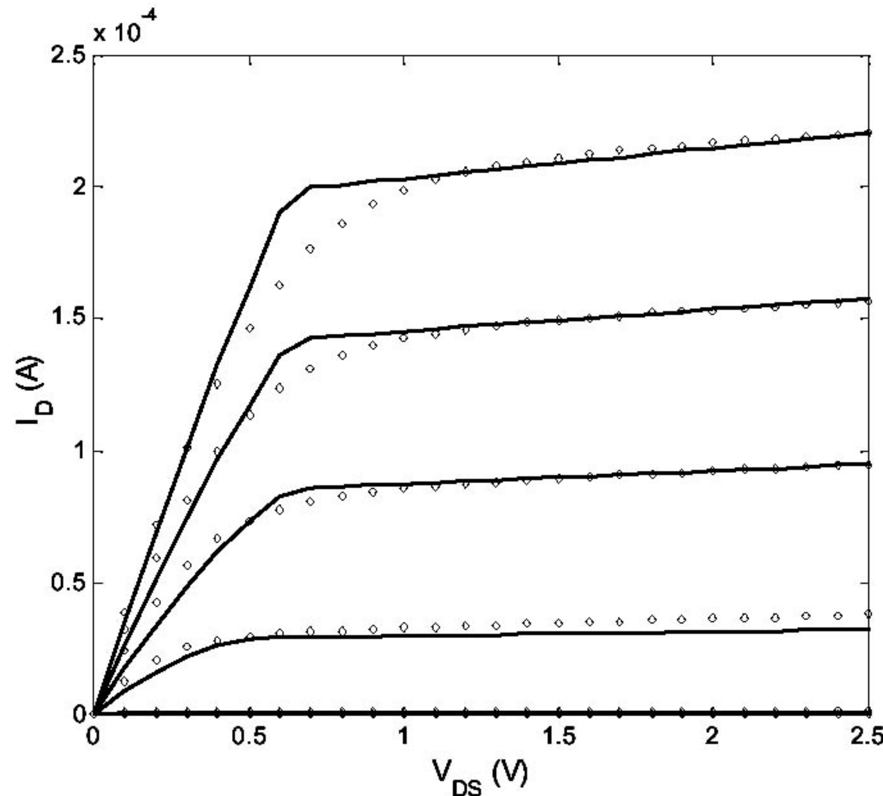
$$I_D = k\left(V_{GT}V_{MIN} - 0.5V_{MIN}^2\right)(1 + \lambda V_{DS}) \quad \text{for } V_{GT} \geq 0$$

$$= 0 \quad \text{for } V_{GT} \leq 0$$

$$V_{MIN} = MIN(V_{DS}, V_{GT}, V_{DSAT})$$

$$V_{GT} = V_{GS} - V_T, \qquad V_T = V_{T0} + \gamma\left(\sqrt{|-2\phi_F + V_{SB}|} - \sqrt{|-2\phi_F|}\right)$$

MOS Model Comparison

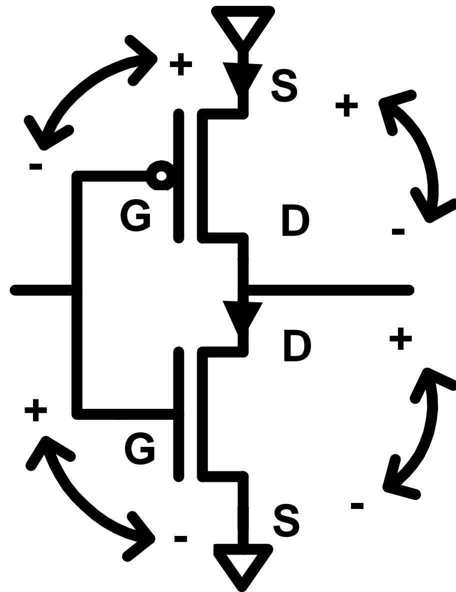


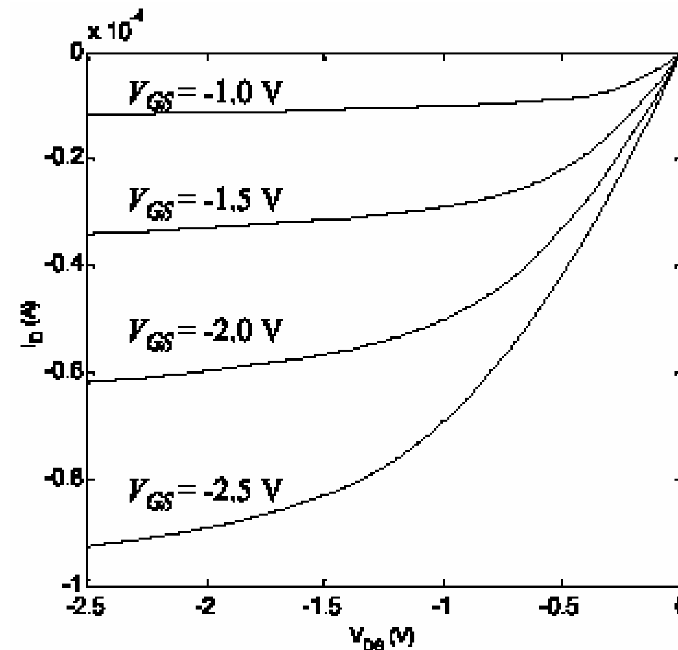
Solid line: simple model

Dotted line: SPICE simulation

- Many more far more advanced models do exist (BSIM4 ~ 20k lines of C)
- Are only suited for computer simulation
- The SPICE simulator is the 'good old' workhorse of the industry
- Reliable, but low speed

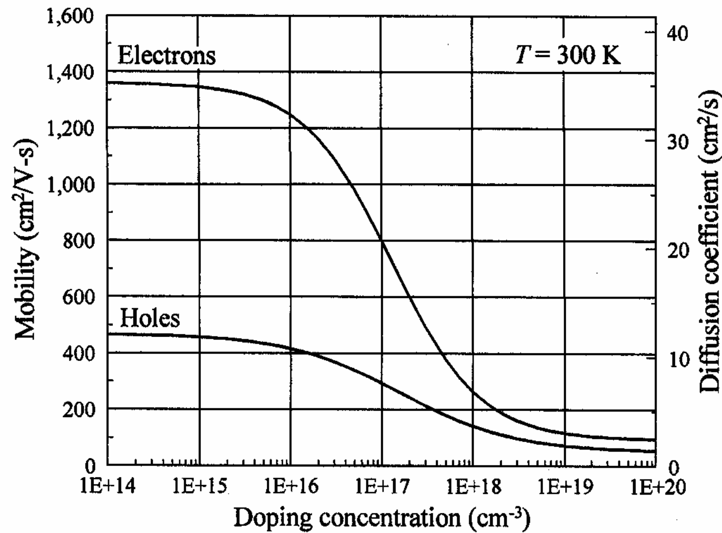
NMOS vs. PMOS

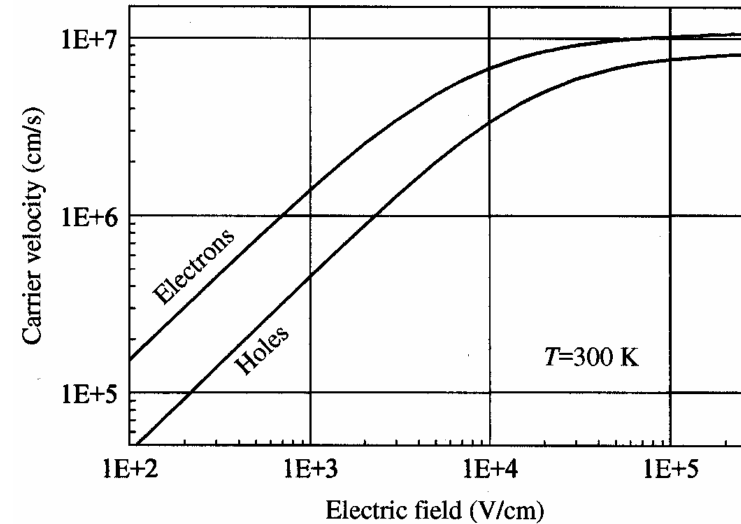




- PMOS (V_{DS}, V_{GS}, I_D, V_T) < 0
- Can calculate as if NMOS using absolute values
- PMOS device not as strong as NMOS

NMOS vs. PMOS (2)





Zero-field mobility (bulk!) **Velocity vs. Field**

$\mu_p < \mu_n \quad \Rightarrow \quad k'_p < k'_n$

$v_{sat_p} \approx v_{sat_n} \quad \Rightarrow \quad |V_{DSAT_p}| > |V_{DSAT_n}|$

	V_{T0} (V)	γ ($V^{0.5}$)	V_{DSAT} (V)	k' (A/V^2)	λ (V^{-1})
NMOS	0.43	0.4	0.63	115×10^{-6}	0.06
PMOS	–0.4	-0.4	-1	-30×10^{-6}	-0.1

Alternative Saturation Expression

- **Saturation if** $V_{DS} > V_{GS} - V_T$
- **Show that** $V_{DS} > V_{GS} - V_T \Leftrightarrow V_{GD} < V_T$
- **Proof:**

$$V_{DS} > V_{GS} - V_T$$
$$\Leftrightarrow V_D - V_S > V_G - V_S - V_T$$
$$\Leftrightarrow V_D > V_G - V_T$$
$$\Leftrightarrow V_G - V_T < V_D$$
$$\Leftrightarrow V_G - V_D < V_T$$
$$\Leftrightarrow V_{GD} < V_T$$

Physically this relates to 'amount of inversion' at drain side

If inversion at drain side disappears: pinch-off

- **This is an alternative expression for the saturation region**
- **Can be handy**

MOS Device Symmetry

- MOS transistors are symmetrical
- Strong inversion at source if $V_{GS} > V_T$
- Strong inversion at drain if $V_{GD} > V_T$

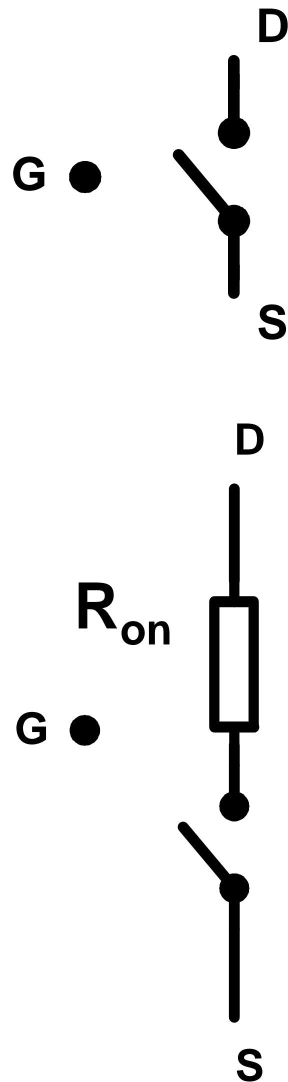
Independent!

- You should check the I-V relations when interchanging drain and source
- Identification of source drain only by convention
- Determined by circuit-environment

	NMOS	PMOS	General
Source	V_{SS}-side	V_{DD}-side	Strongest inversion
Drain	V_{DD}-side	V_{SS}-side	Weakest inversion

V_{SS}: low supply voltage, V_{DD} = high supply voltage

Improved MOS Transistor Switch Level Model



Position of switch depends on gate to source voltage

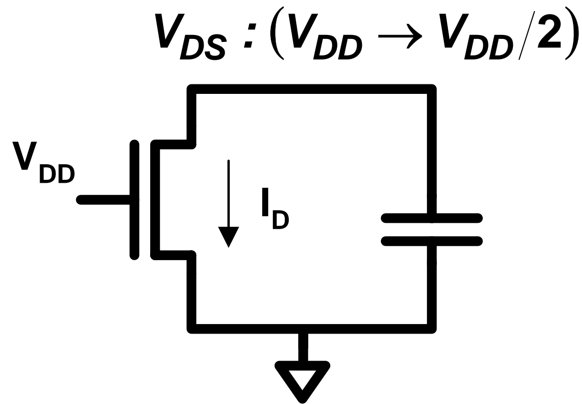
V_{GS}	NMOS	PMOS
hi	closed	open
lo	open	closed

More detailed model may include R_{on}

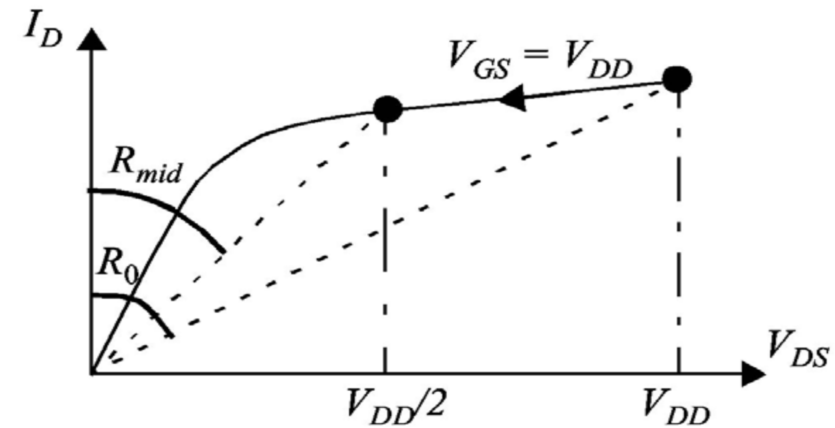
- R_{on} is highly non-linear
- Make linear approximation R_{eq}
- Model with (linear) R_{eq} less detailed then previous equation based model, but often useful for first estimates of behavior

Switch Model R_{on}

$V_{DS} : (V_{DD} \rightarrow V_{DD}/2)$



(a) Schematic



(b) trajectory traversed on ID-VDS curve.

$$R_{eq} = \frac{1}{2}\left[\frac{V_{DD}}{I_{DSAT}(1+\lambda V_{DD})} + \frac{V_{DD}/2}{I_{DSAT}(1+\lambda V_{DD}/2)}\right]$$

$$\frac{1}{1+\lambda V_{DD}} \approx 1 - \lambda V_{DD} + O(\lambda^2 Vdd^2)$$

2.3% error with

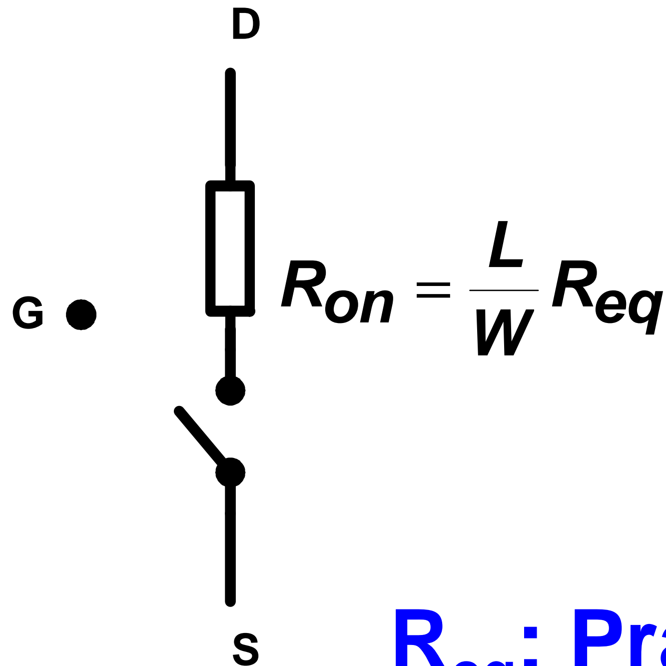
$\lambda = 0.06\ V^{-1}, V_{DD} = 2.5V$

$$R_{eq} \approx \frac{1}{2}\frac{V_{DD}}{I_{DSAT}}\left[\left(1 - \lambda V_{DD} + \frac{1}{2}(1 - \lambda V_{DD}/2)\right)\right]$$

$$= \frac{3}{4}\frac{V_{DD}}{I_{DSAT}}\left[1 - \frac{5}{6}\lambda V_{DD}\right]$$

Theory!

MOS Transistor
Switch Level Model (Empirical).



$$R_{on} = \frac{L}{W} R_{eq}$$

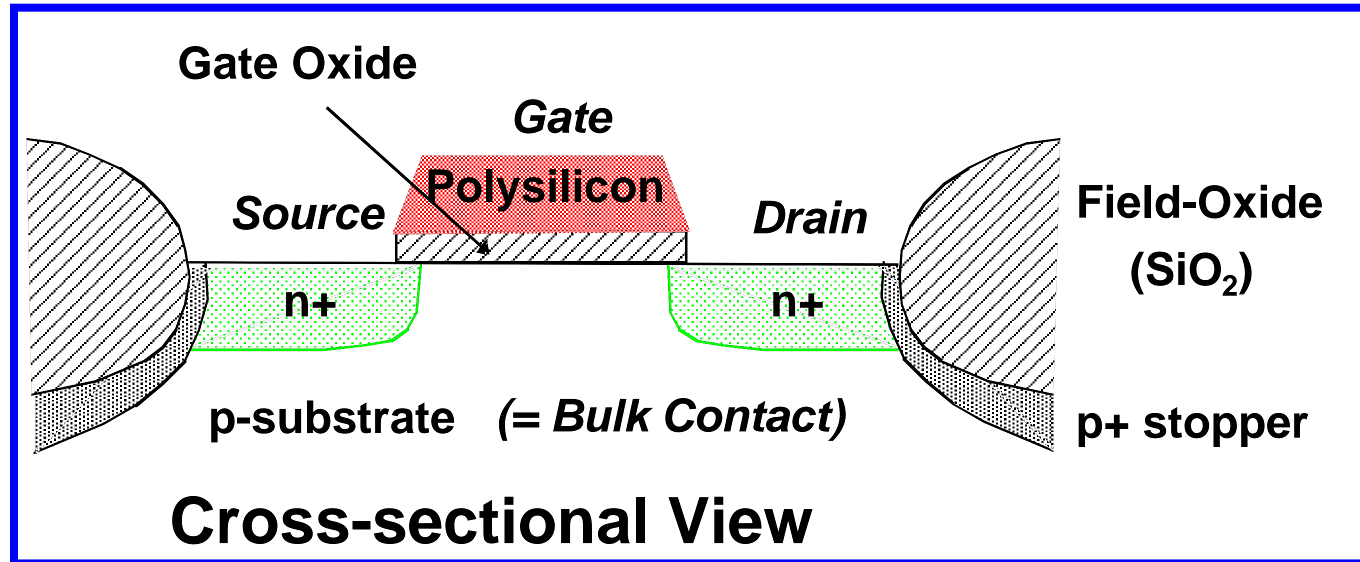
Position of switch depends on gate to source voltage

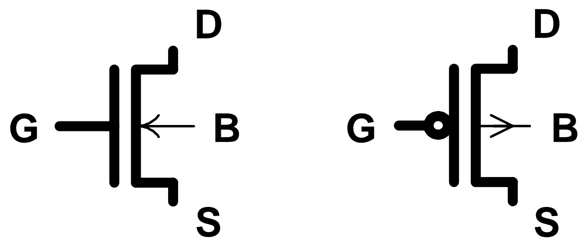
V_{GS}	NMOS	PMOS
hi	closed	open
lo	open	closed

R_{eq}: Practice!

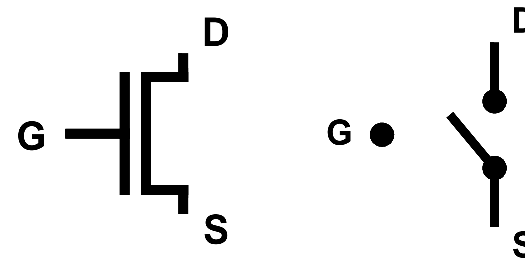
R_{eq} \ V_{dd} (V)	1	1.5	2	2.5
NMOS (kΩ)	35	19	15	13
PMOS (kΩ)	115	55	38	31

The MOS Transistor Summary





Schematic symbols, very often w/o bulk contact

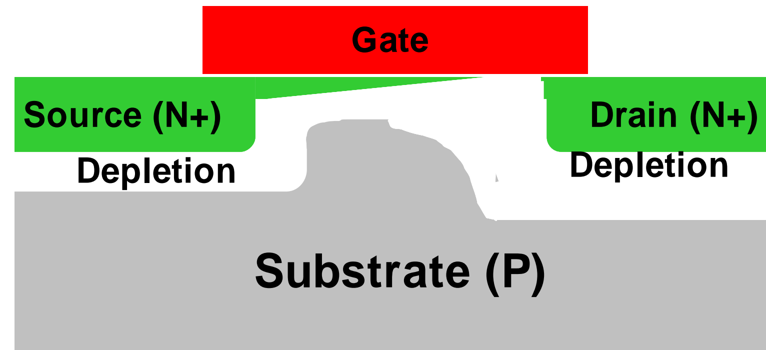


Switch closed if $V_{GS} > V_T$

Simplest possible equiv. ckt.

The MOS Transistor Summary ctd.

- Need to **analyze** speed, power, noise etc of MOS circuits
- Simple switch-level model **not sufficient**
- Study exact operation to derive **more precise IV relations**



$$I_D = k\left(V_{GT}V_{MIN} - 0.5V_{MIN}^2\right)\left(1+\lambda V_{DS}\right) \qquad \text{for } V_{GT} \geq 0$$

$$= 0 \qquad \text{for } V_{GT} \leq 0$$

$$V_{MIN} = MIN\left(V_{DS}, V_{GT}, V_{DSAT}\right)$$

$$V_{GT} = V_{GS} - V_T, \qquad V_T = V_{T0} + \gamma\left(\sqrt{\left|-2\phi_F + V_{SB}\right|} - \sqrt{\left|-2\phi_F\right|}\right)$$

Summary

- Semiconductor Physics
- The diode
  - Depletion, I-V relations, capacitance, secondary effects, models
- The MOS transistor
  - First glance, threshold, I-V relations, models
  - Dynamic behavior (capacitances), resistances, more Second-Order effects, models